

EUROPEAN PATENT OFFICE
U.S. PATENT AND TRADEMARK OFFICE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

The following classification changes will be effected by this Notice of Changes:

<u>Action</u>	<u>Subclass</u>	<u>Group(s)</u>
SCHEME:		
Symbols Deleted:	H01L	27/14, 27/142, 27/1421, 27/144, 27/1443, 27/1446, 27/146, 27/14601, 27/14603, 27/14605, 27/14607, 27/14609, 27/1461, 27/14612, 27/14614, 27/14616, 27/14618, 27/1462, 27/14621, 27/14623, 27/14625, 27/14627, 27/14629, 27/1463, 27/14632, 27/14634, 27/14636, 27/14638, 27/1464, 27/14641, 27/14643, 27/14645, 27/14647, 27/14649, 27/1465, 27/14652, 27/14654, 27/14656, 27/14658, 27/14659, 27/14661, 27/14663, 27/14665, 27/14667, 27/14669, 27/1467, 27/14672, 27/14674, 27/14676, 27/14678, 27/14679, 27/14681, 27/14683, 27/14685, 27/14687, 27/14689, 27/1469, 27/14692, 27/14694, 27/14696, 27/14698, 27/148, 27/14806, 27/14812, 27/14818, 27/14825, 27/14831, 27/14837, 27/14843, 27/1485, 27/14856, 27/14862, 27/14868, 27/14875, 27/14881, 27/14887, 27/14893
	H01L	31/00, 31/02, 31/02002, 31/02005, 31/02008, 31/0201, 31/02013, 31/02016, 31/02019, 31/02021, 31/02024, 31/02027, 31/0203, 31/0216, 31/02161, 31/02162, 31/02164, 31/02165, 31/02167, 31/02168, 31/0224, 31/022408, 31/022416, 31/022425, 31/022433, 31/022441, 31/02245, 31/022458, 31/022466, 31/022475, 31/022483, 31/022491, 31/0232, 31/02322, 31/02325, 31/02327, 31/0236, 31/02363, 31/02366, 31/024, 31/0248, 31/0256, 31/0264, 31/0272, 31/02725, 31/028, 31/0284, 31/0288, 31/0296, 31/02963, 31/02966, 31/0304, 31/03042, 31/03044, 31/03046, 31/03048, 31/0312, 31/03125, 31/032, 31/0321, 31/0322, 31/0323, 31/0324, 31/0325, 31/0326, 31/0327, 31/0328, 31/0336, 31/03365, 2031/0344, 31/0352, 31/035209, 31/035218, 31/035227, 31/035236, 31/035245, 31/035254, 31/035263, 31/035272, 31/035281, 31/03529, 31/036, 31/0368, 31/03682, 31/03685, 31/03687, 31/0376, 31/03762, 31/03765, 31/03767, 31/0384, 31/03845,

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

		31/0392, 31/03921, 31/03923, 31/03925, 31/03926, 31/03928, 31/04, 31/041, 31/042, 31/043, 31/044, 31/0443, 31/0445, 31/046, 31/0463, 31/0465, 31/0468, 31/047, 31/0475, 31/048, 31/0481, 31/0488, 31/049, 31/05, 31/0504, 31/0508, 31/0512, 31/0516, 31/052, 31/0521, 31/0525, 31/053, 31/054, 31/0543, 31/0547, 31/0549, 31/055, 31/056, 31/06, 31/061, 31/062, 31/065, 31/068, 31/0682, 31/0684, 31/0687, 31/06875, 31/0693, 31/07, 31/072, 31/0725, 31/073, 31/0735, 31/074, 31/0745, 31/0747, 31/0749, 31/075, 31/076, 31/077, 31/078, 31/08, 31/085, 31/09, 31/095, 31/10, 31/101, 31/1013, 31/1016, 31/102, 31/1025, 31/103, 31/1032, 31/1035, 31/1037, 31/105, 31/1055, 31/107, 31/1075, 31/108, 31/1085, 31/109, 31/11, 31/1105, 31/111, 31/1113, 31/1116, 31/112, 31/1121, 31/1122, 31/1123, 31/1124, 31/1125, 31/1126, 31/1127, 31/1128, 31/1129, 31/113, 31/1133, 31/1136, 31/115, 31/117, 31/1175, 31/118, 31/1185, 31/119, 31/12, 31/125, 31/14, 31/141, 31/143, 31/145, 31/147, 31/153, 31/16, 31/161, 31/162, 31/164, 31/165, 31/167, 31/173, 31/18, 31/1804, 31/1808, 31/1812, 31/1816, 31/182, 31/1824, 31/1828, 31/1832, 31/1836, 31/184, 31/1844, 31/1848, 31/1852, 31/1856, 31/186, 31/1864, 31/1868, 31/1872, 31/1876, 31/188, 31/1884, 31/1888, 31/1892, 31/1896, 31/20, 31/202, 31/204, 31/206, 31/208
Symbols New:	H10F	SUBCLASS
	H10F	10/00, 10/10, 10/11, 10/12, 10/13, 10/14, 10/142, 10/1425, 10/144, 10/146, 10/148, 10/16, 10/161, 10/162, 10/163, 10/164, 10/165, 10/166, 10/167, 10/169, 10/17, 10/172, 10/174, 10/18, 10/19
	H10F	19/00, 19/10, 19/20, 19/30, 19/31, 19/33, 19/35, 19/37, 19/40, 19/50, 19/70, 19/75, 19/80, 19/804, 19/807, 19/85, 19/90, 19/902, 19/904, 19/906, 19/908
	H10F	30/00, 30/10, 30/15, 30/20, 30/21, 30/22, 30/2205, 30/221, 30/2212, 30/2215, 30/2218, 30/222, 30/223, 30/2235, 30/225, 30/2255, 30/227, 30/2275, 30/24, 30/245, 30/26, 30/263, 30/2635, 30/28, 30/282, 30/2823, 30/283, 30/2837,

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

		30/2843, 30/285, 30/2857, 30/2863, 30/287, 30/2873, 30/2877, 30/288, 30/289, 30/29, 30/292, 30/2925, 30/295, 30/2955, 30/298, 30/301
	H10F	39/00, 39/011, 39/014, 39/016, 39/018, 39/021, 39/022, 39/024, 39/026, 39/028, 39/10, 39/103, 39/107, 39/12, 39/15, 39/151, 39/1515, 39/152, 39/153, 39/1532, 39/1534, 39/1536, 39/1538, 39/154, 39/156, 39/157, 39/1575, 39/158, 39/159, 39/18, 39/182, 39/1825, 39/184, 39/1843, 39/1847, 39/186, 39/1865, 39/189, 39/1892, 39/1895, 39/1898, 39/191, 39/192, 39/193, 39/1935, 39/194, 39/1945, 39/195, 39/196, 39/197, 39/198, 39/199, 39/80, 39/802, 39/8023, 39/8027, 39/803, 39/8033, 39/8037, 39/80373, 39/80377, 39/804, 39/805, 39/8053, 39/8057, 39/806, 39/8063, 39/8067, 39/807, 39/809, 39/811, 39/812, 39/813, 39/90, 39/95
	H10F	55/00, 55/10, 55/15, 55/155, 55/16, 55/165, 55/17, 55/18, 55/20, 55/205, 55/207, 55/208, 55/25, 55/255, 55/26
	H10F	71/00, 71/10, 71/103, 71/1035, 71/107, 71/121, 71/1212, 71/1215, 71/1218, 71/1221, 71/1224, 71/125, 71/1253, 71/1257, 71/127, 71/1272, 71/1274, 71/1276, 71/1278, 71/128, 71/129, 71/131, 71/132, 71/133, 71/134, 71/135, 71/136, 71/137, 71/1375, 71/138, 71/1385, 71/139, 71/1395
	H10F	77/00, 77/10, 77/12, 77/121, 77/1215, 77/122, 77/1223, 77/1226, 77/1227, 77/1228, 77/123, 77/1233, 77/1237, 77/124, 77/1243, 77/1246, 77/1248, 77/12485, 77/126, 77/1265, 77/127, 77/1275, 77/128, 77/1285, 77/14, 77/143, 77/1433, 77/1437, 77/146, 77/1462, 77/1465, 77/1468, 77/147, 77/148, 77/16, 77/162, 77/1625, 77/164, 77/1642, 77/1645, 77/1648, 77/166, 77/1662, 77/1665, 77/1668, 77/169, 77/1692, 77/1694, 77/1696, 77/1698, 77/1699, 77/20, 77/206, 77/211, 77/215, 77/219, 77/223, 77/227, 77/241, 77/244, 77/247, 77/251, 77/254, 77/30, 77/306, 77/311, 77/315, 77/331, 77/334, 77/337, 77/40, 77/407, 77/413, 77/42, 77/45, 77/48, 77/484, 77/488, 77/492, 77/496, 77/50, 77/60, 77/63, 77/67, 77/68, 77/70, 77/703, 77/707, 77/80, 77/90, 77/93, 77/933, 77/935, 77/937, 77/939, 77/95, 77/953, 77/955, 77/957, 77/959

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

	H10F	99/00
Warnings New:	H01L	SUBCLASS
	H10F	10/00
	H10F	19/00
	H10F	30/00
	H10F	39/00, 39/80, 39/802, 39/803, 39/804, 39/805, 39/806, 39/807, 39/809, 39/811, 39/812, 39/813
	H10F	71/00, 71/10, 71/103, 71/107, 71/128, 71/129, 71/131, 71/132, 71/133, 71/134, 71/135, 71/136, 71/137, 71/138, 71/139
	H10F	99/00
Notes New:	H01L	21/00
	H01L	25/00
	H10F	SUBCLASS
	H10F	77/00, 77/12
Guidance Headings New:	H10F	10/00
	H10F	30/00
	H10F	55/00
	H10F	71/00
DEFINITIONS:		
Definitions Deleted: (no frozen (F) symbol definitions should be deleted)	H01L	27/14, 27/142, 27/144, 27/1443, 27/1446, 27/146, 27/14601, 27/14603, 27/14605, 27/14607, 27/14609, 27/1461, 27/14612, 27/14614, 27/14616, 27/14618, 27/1462, 27/14621, 27/14623, 27/14625, 27/14627, 27/14629, 27/1463, 27/14632, 27/14634, 27/14636, 27/14638, 27/1464, 27/14641, 27/14643, 27/14645, 27/14647, 27/14649, 27/1465, 27/14652, 27/14654, 27/14656, 27/14658, 27/14659, 27/14661, 27/14663, 27/14665, 27/1467, 27/14672, 27/14674, 27/14676, 27/14678, 27/14683, 27/14685, 27/14687, 27/14689, 27/1469, 27/148, 27/14812, 27/14818, 27/14825, 27/14831, 27/14837, 27/14843, 27/1485, 27/14856, 27/14862
	H01L	31/00, 31/02, 31/02002, 31/02005, 31/02008, 31/02016, 31/02021, 31/02024, 31/02027, 31/0203, 31/0216, 31/02161, 31/02162, 31/02164, 31/02165, 31/02167, 31/02168, 31/0224, 31/022408, 31/022425, 31/022433, 31/022466, 31/0232, 31/02322, 31/0236, 31/024, 31/0248, 31/0256, 31/0264, 31/028, 31/0284, 31/02966, 31/03046, 31/0321, 31/0322, 31/03365, 31/0352, 31/035236, 31/035272, 31/035281, 31/03529, 31/036,

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

		31/0368, 31/03682, 31/0376, 31/03762, 31/03767, 31/0384, 31/0392, 31/03921, 31/04, 31/041, 31/042, 31/044, 31/0443, 31/0445, 31/046, 31/0463, 31/0465, 31/0468, 31/047, 31/0475, 31/048, 31/049, 31/05, 31/052, 31/0525, 31/053, 31/054, 31/055, 31/056, 31/06, 31/061, 31/062, 31/065, 31/068, 31/0687, 31/0693, 31/07, 31/072, 31/0725, 31/073, 31/0735, 31/074, 31/0745, 31/0747, 31/0749, 31/075, 31/076, 31/077, 31/078, 31/08, 31/085, 31/09, 31/10, 31/101, 31/103, 31/12, 31/125, 31/14, 31/147, 31/153, 31/16, 31/18, 31/1804, 31/1828, 31/184, 31/186, 31/1864, 31/1868, 31/1872, 31/1876, 31/188, 31/1884, 31/20, 31/202, 31/206, 31/208
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The following subclasses/groups are also impacted by this Notice of Changes (indicate subclasses/groups outside of the project scope, such as those listed in the CRL):

B32B, B60H, B60L, B60R, B64G, B65B, C01G, C03C, C04B, C09J, C23C, C25D, E04D, F21S, F24F, F24S, G01B, G01J, G01S, G01T, G01V, G02B, G02F, G03B, G06E, G06V, G08G, G21H, H01C, H01G, H01J, H01L, H01M, H01Q, H01S, H02H, H02J, H02S, H04B, H04N, H05B, H05K, H10K, H10N

This Notice of Changes includes the following [Check the ones included]:

1. CLASSIFICATION SCHEME CHANGES

- A. New, Modified or Deleted Group(s)
- B. New, Modified or Deleted Warning(s)
- C. New, Modified or Deleted Note(s)
- D. New, Modified or Deleted Guidance Heading(s)

2. DEFINITIONS

- A. New or Modified Definitions (Full definition template)
- B. Modified or Deleted Definitions (Definitions Quick Fix)

3. REVISION CONCORDANCE LIST (RCL)

4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

5. CHANGES TO THE CROSS-REFERENCE LIST (CRL)

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

1. CLASSIFICATION SCHEME CHANGES

A. New, Modified or Deleted Group(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L27/14	1	including semiconductor components sensitive to infrared radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation (radiation-sensitive components structurally associated with one or more electric light sources only H01L 31/14; couplings of light guides with optoelectronic elements G02B 6/42)	<administrative transfer to H10F 99/00>
D	H01L27/142	2	Energy conversion devices (photovoltaic modules or arrays of single photovoltaic cells comprising bypass diodes integrated or directly associated with the devices H01L 31/0443; photovoltaic modules composed of a plurality of thin film solar cells deposited on the same substrate H01L 31/046)	<administrative transfer to H10F 19/50>
D	H01L 27/1421	3	{comprising bypass diodes integrated or directly associated with the device, e.g. bypass diode integrated or formed in or on the same substrate as the solar cell}	<administrative transfer to H10F 19/75>
D	H01L27/144	2	Devices controlled by radiation	<administrative transfer to H10F 39/10>
D	H01L 27/1443	3	{with at least one potential jump or surface barrier}	<administrative transfer to H10F 39/103>
D	H01L 27/1446	3	{in a repetitive configuration}	<administrative transfer to H10F 39/107 >
D	H01L27/146	3	Imager structures	<administrative transfer to H10F 39/12>
D	H01L 27/14601	4	{Structural or functional details thereof}	<administrative transfer to H10F 39/80>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 27/14603	5	{Special geometry or disposition of pixel-elements, address-lines or gate-electrodes}	<administrative transfer to H10F 39/802>
D	H01L 27/14605	6	{Structural or functional details relating to the position of the pixel elements, e.g. smaller pixel elements in the center of the imager compared to pixel elements at the periphery}	<administrative transfer to H10F 39/8023>
D	H01L 27/14607	6	{Geometry of the photosensitive area}	<administrative transfer to H10F 39/8027>
D	H01L 27/14609	5	{Pixel-elements with integrated switching, control, storage or amplification elements (scanning details of imagers (circuitry of solid-state image sensors H04N 25/00); circuitry of imagers H04N 25/70)}	<administrative transfer to H10F 39/803>
D	H01L 27/1461	6	{characterised by the photosensitive area}	<administrative transfer to H10F 39/8033>
D	H01L 27/14612	6	{involving a transistor}	<administrative transfer to H10F 39/8037>
D	H01L 27/14614	7	{having a special gate structure}	<administrative transfer to H10F 39/80373>
D	H01L 27/14616	7	{characterised by the channel of the transistor, e.g. channel having a doping gradient}	<administrative transfer to H10F 39/80377>
D	H01L 27/14618	5	{Containers}	<administrative transfer to H10F 39/804>
D	H01L 27/1462	5	{Coatings}	<administrative transfer to H10F 39/805>
D	H01L 27/14621	6	{Colour filter arrangements}	<administrative transfer to H10F 39/8053>
D	H01L 27/14623	6	{Optical shielding}	<administrative transfer to H10F 39/8057>
D	H01L 27/14625	5	{Optical elements or arrangements associated with the device}	<administrative transfer to H10F 39/806>
D	H01L 27/14627	6	{Microlenses}	<administrative transfer to H10F 39/8063>
D	H01L 27/14629	6	{Reflectors}	<administrative transfer to H10F 39/8067>
D	H01L 27/1463	5	{Pixel isolation structures}	<administrative transfer to H10F 39/807>
D	H01L 27/14632	5	{Wafer-level processed structures}	<administrative transfer to H10F 39/026>
D	H01L 27/14634	5	{Assemblies, i.e. Hybrid structures}	<administrative transfer to H10F 39/809>
D	H01L 27/14636	5	{Interconnect structures}	<administrative transfer to H10F 39/811>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 27/14638	5	{Structures specially adapted for transferring the charges across the imager perpendicular to the imaging plane}	<administrative transfer to H10F 39/812>
D	H01L 27/1464	5	{Back illuminated imager structures}	<administrative transfer to H10F 39/199>
D	H01L 27/14641	5	{Electronic components shared by two or more pixel-elements, e.g. one amplifier shared by two pixel elements}	<administrative transfer to H10F 39/813>
D	H01L 27/14643	4	{Photodiode arrays; MOS imagers}	<administrative transfer to H10F 39/18>
D	H01L 27/14645	5	{Colour imagers}	<administrative transfer to H10F 39/182>
D	H01L 27/14647	6	{Multicolour imagers having a stacked pixel-element structure, e.g. npn, npnp or MQW elements}	<administrative transfer to H10F 39/1825>
D	H01L 27/14649	5	{Infrared imagers}	<administrative transfer to H10F 39/184>
D	H01L 27/1465	6	{of the hybrid type}	<administrative transfer to H10F 39/1843>
D	H01L 27/14652	6	{Multispectral infrared imagers, having a stacked pixel-element structure, e.g. npn, npnp or MQW structures}	<administrative transfer to H10F 39/1847>
D	H01L 27/14654	5	{Blooming suppression}	<administrative transfer to H10F 39/186>
D	H01L 27/14656	6	{Overflow drain structures}	<administrative transfer to H10F 39/1865>
D	H01L 27/14658	5	{X-ray, gamma-ray or corpuscular radiation imagers (measuring X-, gamma- or corpuscular radiation G01T 1/00)}	<administrative transfer to H10F 39/189>
D	H01L 27/14659	6	{Direct radiation imager structures}	<administrative transfer to H10F 39/1892>
D	H01L 27/14661	6	{of the hybrid type}	<administrative transfer to H10F 39/1895>
D	H01L 27/14663	6	{Indirect radiation imagers, e.g. using luminescent members}	<administrative transfer to H10F 39/1898>
D	H01L 27/14665	4	{Imagers using a photoconductor layer}	<administrative transfer to H10F 39/191>
D	H01L 27/14667	5	{Colour imagers}	<administrative transfer to H10F 39/192>
D	H01L 27/14669	5	{Infrared imagers}	<administrative transfer to H10F 39/193>
D	H01L 27/1467	6	{of the hybrid type}	<administrative transfer to H10F 39/1935>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	Transferred to#
D	H01L 27/14672	5	{Blooming suppression}	<administrative transfer to H10F 39/194>
D	H01L 27/14674	6	{Overflow drain structures}	<administrative transfer to H10F 39/1945>
D	H01L 27/14676	5	{X-ray, gamma-ray or corpuscular radiation imagers (measuring X-, gamma- or corpuscular radiation G01T 1/00)}	<administrative transfer to H10F 39/195>
D	H01L 27/14678	4	{Contact-type imagers}	<administrative transfer to H10F 39/198>
D	H01L 27/14679	4	{Junction field effect transistor [JFET] imagers; static induction transistor [SIT] imagers}	<administrative transfer to H10F 39/196>
D	H01L 27/14681	4	{Bipolar transistor imagers}	<administrative transfer to H10F 39/197>
D	H01L 27/14683	4	{Processes or apparatus peculiar to the manufacture or treatment of these devices or parts thereof (not peculiar thereto H01L 21/00)}	<administrative transfer to H10F 39/011>
D	H01L 27/14685	5	{Process for coatings or optical elements}	<administrative transfer to H10F 39/024>
D	H01L 27/14687	5	{Wafer level processing}	<administrative transfer to H10F 39/026>
D	H01L 27/14689	5	{MOS based technologies}	<administrative transfer to H10F 39/014>
D	H01L 27/1469	5	{Assemblies, i.e. hybrid integration}	<administrative transfer to H10F 39/018>
D	H01L 27/14692	5	{Thin film technologies, e.g. amorphous, poly, micro- or nanocrystalline silicon}	<administrative transfer to H10F 39/016>
D	H01L 27/14694	5	{The active layers comprising only A _{III} B _V compounds, e.g. GaAs, InP}	<administrative transfer to H10F 39/021>
D	H01L 27/14696	5	{The active layers comprising only A _{II} B _{VI} compounds, e.g. CdS, ZnS, CdTe}	<administrative transfer to H10F 39/022>
D	H01L 27/14698	5	{Post-treatment for the devices, e.g. annealing, impurity-gettering, short-circuit elimination, recrystallisation}	<administrative transfer to H10F 39/028>
D	H01L27/148	4	Charge coupled imagers {(individual charge coupled devices H01L29/765)}	<administrative transfer to H10F 39/15>
D	H01L 27/14806	5	{Structural or functional details thereof}	<administrative transfer to H10F 39/80>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 27/14812	6	{Special geometry or disposition of pixel-elements, address lines or gate-electrodes}	<administrative transfer to H10F 39/151>
D	H01L 27/14818	7	{Optical shielding}	<administrative transfer to H10F 39/1515>
D	H01L 27/14825	5	{Linear CCD imagers}	<administrative transfer to H10F 39/152>
D	H01L 27/14831	5	{Area CCD imagers}	<administrative transfer to H10F 39/153>
D	H01L 27/14837	6	{Frame-interline transfer}	<administrative transfer to H10F 39/1532>
D	H01L 27/14843	6	{Interline transfer}	<administrative transfer to H10F 39/1534>
D	H01L 27/1485	6	{Frame transfer}	<administrative transfer to H10F 39/1536>
D	H01L 27/14856	6	{Time-delay and integration}	<administrative transfer to H10F 39/1538>
D	H01L 27/14862	5	{CID imagers}	<administrative transfer to H10F 39/154>
D	H01L 27/14868	5	{CCD or CID colour imagers}	<administrative transfer to H10F 39/156>
D	H01L 27/14875	5	{Infrared CCD or CID imagers}	<administrative transfer to H10F 39/157>
D	H01L 27/14881	6	{of the hybrid type}	<administrative transfer to H10F 39/1575>
D	H01L 27/14887	5	{Blooming suppression}	<administrative transfer to H10F 39/158>
D	H01L 27/14893	5	{comprising a photoconductive layer deposited on the CCD structure}	<administrative transfer to H10F 39/159>
D	H01L 31/00	0	Semiconductor devices sensitive to infrared radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof (H10K30/00 takes precedence; devices consisting of a plurality of solid state components formed in, or on, a common substrate, other than combinations of radiation-sensitive	<administrative transfer to H10F99/00>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
			components with one or more electric light sources, H01L27/00)	
D	H01L 31/02	1	Details	<administrative transfer to H10F 77/00>
D	H01L 31/02002	2	{Arrangements for conducting electric current to or from the device in operations}	<administrative transfer to H10F 77/93>
D	H01L 31/02005	3	{for device characterised by a least one potential jump barrier or surface barrier}	<administrative transfer to H10F 77/933>
D	H01L 31/02008	4	{for solar cells or solar cell modules}	<administrative transfer to H10F 77/935>
D	H01L 31/0201	5	{comprising specially adapted module bus-bar structures}	<administrative transfer to H10F 77/937>
D	H01L 31/02013	5	{comprising output lead wires elements}	<administrative transfer to H10F 77/939>
D	H01L 31/02016	2	{Circuit arrangements of general character for the devices}	<administrative transfer to H10F 77/95>
D	H01L 31/02019	3	{for devices characterised by at least one potential jump barrier or surface barrier}	<administrative transfer to H10F 77/953>
D	H01L 31/02021	4	{for solar cells (electrical connection means, e.g. junction boxes, specially adapted for structural association with photovoltaic modules H02S 40/34)}	<administrative transfer to H10F 77/955>
D	H01L 31/02024	4	{Position sensitive and lateral effect photodetectors; Quadrant photodiodes}	<administrative transfer to H10F 77/957>
D	H01L 31/02027	4	{for devices working in a avalanche mode}	<administrative transfer to H10F 77/959>
D	H01L 31/0203	2	Containers; Encapsulations {, e.g. encapsulation of photodiodes}(for photovoltaic devices H01L 31/048; for organic photosensitive devices H10K 30/80)	<administrative transfer to H10F 77/50>
D	H01L 31/0216	2	Coatings (H01L 31/041 takes precedence)	<administrative transfer to H10F 77/30>
D	H01L 31/02161	3	{for devices characterised by a least one potential jump barrier or surface barrier}	<administrative transfer to H10F 77/306>
D	H01L 31/02162	4	{for filtering or shielding light, e.g. multicolour filters for photodetectors}	<administrative transfer to H10F 77/331>
D	H01L 31/02164	5	{for shielding light, e.g. light blocking layers, cold shields for infrared detectors}	<administrative transfer to H10F 77/334>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/02165	5	{using interference filters, e.g. multilayer dielectric filters (interference filters G02B 5/28)}	<administrative transfer to H10F 77/337>
D	H01L 31/02167	4	{for solar cells}	<administrative transfer to H10F 77/311>
D	H01L 31/02168	5	{the coatings being antireflective or having enhancing optical properties for the solar cells}	<administrative transfer to H10F 77/315>
D	H01L 31/0224	2	Electrodes	<administrative transfer to H10F 77/20>
D	H01L 31/022408	3	{for devices characterised by at least one potential jump barrier or surface barrier}	<administrative transfer to H10F 77/206>
D	H01L 31/022416	4	{comprising ring electrodes}	<administrative transfer to H10F 77/241>
D	H01L 31/022425	4	{for solar cells}	<administrative transfer to H10F 77/211>
D	H01L 31/022433	5	{Particular geometry of the grid contacts}	<administrative transfer to H10F 77/215>
D	H01L 31/022441	5	{Electrode arrangements specially adapted for back-contact solar cells}	<administrative transfer to H10F 77/219>
D	H01L 31/02245	6	{for metallisation wrap-through [MWT] type solar cells}	<administrative transfer to H10F 77/223>
D	H01L 31/022458	6	{for emitter wrap-through [EWT] type solar cells, e.g. interdigitated emitter-base back-contacts}	<administrative transfer to H10F 77/227>
D	H01L 31/022466	3	{made of transparent conductive layers, e.g. TCO, ITO layers}	<administrative transfer to H10F 77/244>
D	H01L 31/022475	4	{composed of indium tin oxide [ITO]}	<administrative transfer to H10F 77/247>
D	H01L 31/022483	4	{composed of zinc oxide [ZnO]}	<administrative transfer to H10F 77/251>
D	H01L 31/022491	4	{composed of a thin transparent metal layer, e.g. gold}	<administrative transfer to H10F 77/254>
D	H01L 31/0232	2	Optical elements or arrangements associated with the device (H01L 31/0236 takes precedence; for photovoltaic cells H01L 31/054; for photovoltaic modules H02S 40/20)	<administrative transfer to H10F 77/40>
D	H01L 31/02322	3	{comprising luminescent members, e.g. fluorescent sheets upon the device}	<administrative transfer to H10F 77/496>
D	H01L 31/02325	3	{the optical elements not being integrated nor being directly associated with the device}	<administrative transfer to H10F 77/407>
D	H01L 31/02327	3	{the optical elements being integrated or being directly	<administrative transfer to H10F 77/413>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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			associated to the device, e.g. back reflectors (optical coatings H01L 31/0216)}	
D	H01L 31/0236	2	Special surface textures	<administrative transfer to H10F 77/70>
D	H01L 31/02363	3	{of the semiconductor body itself, e.g. textured active layers}	<administrative transfer to H10F 77/703>
D	H01L 31/02366	3	{of the substrate or of a layer on the substrate, e.g. textured ITO/glass substrate or superstrate, textured polymer layer on glass substrate}	<administrative transfer to H10F 77/707>
D	H01L 31/024	2	Arrangements for cooling, heating, ventilating or temperature compensation (for photovoltaic devices H01L 31/052)	<administrative transfer to H10F 77/60>
D	H01L 31/0248	1	characterised by their semiconductor bodies	<administrative transfer to H10F 77/10>
D	H01L 31/0256	2	characterised by the material	<administrative transfer to H10F 77/12>
D	H01L 31/0264	3	Inorganic materials	<administrative transfer to H10F 77/12>
D	H01L 31/0272	4	Selenium or tellurium	<administrative transfer to H10F 77/121>
D	H01L 31/02725	5	{characterised by the doping material}	<administrative transfer to H10F 77/1215>
D	H01L 31/028	4	including, apart from doping material or other impurities, only elements of Group IV of the Periodic Table	<administrative transfer to H10F 77/122>
D	H01L 31/0284	5	{comprising porous silicon as part of the active layer(s) (porous silicon as an antireflective layer for photodiodes H01L 31/0216; for solar cells H01L 31/02168)}	<administrative transfer to H10F 77/1228>
D	H01L 31/0288	5	characterised by the doping material	<administrative transfer to H10F 77/1223>
D	H01L 31/0296	4	including, apart from doping material or other impurities, only A _{II} B _{VI} compounds, e.g. CdS, ZnS, HgCdTe	<administrative transfer to H10F 77/123>
D	H01L 31/02963	5	{characterised by the doping material}	<administrative transfer to H10F 77/1233>
D	H01L 31/02966	5	{including ternary compounds, e.g. HgCdTe}	<administrative transfer to H10F 77/1237>
D	H01L 31/0304	4	including, apart from doping materials or other impurities, only A _{III} B _V compounds	<administrative transfer to H10F 77/124>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/03042	5	{characterised by the doping material}	<administrative transfer to H10F 77/1243>
D	H01L 31/03044	5	{comprising a nitride compounds, e.g. GaN}	<administrative transfer to H10F 77/1246>
D	H01L 31/03046	5	{including ternary or quaternary compounds, e.g. GaAlAs, InGaAs, InGaAsP}	<administrative transfer to H10F 77/1248>
D	H01L 31/03048	6	{comprising a nitride compounds, e.g. InGaN}	<administrative transfer to H10F 77/12485>
D	H01L 31/0312	4	including, apart from doping materials or other impurities, only $A_{IV}B_{IV}$ compounds, e.g. SiC	<administrative transfer to H10F 77/1226>
D	H01L 31/03125	5	{characterised by the doping material}	<administrative transfer to H10F 77/1227>
D	H01L 31/032	4	including, apart from doping materials or other impurities, only compounds not provided for in groups H01L 31/0272 - H01L 31/0312	<administrative transfer to H10F 77/12>
D	H01L 31/0321	5	{characterised by the doping material (H01L 31/0323, H01L 31/0325 take precedence)}	<administrative transfer to H10F 77/12>
D	H01L 31/0322	5	{comprising only $A_{IV}B_{III}C_{VI}$ chalcopyrite compounds, e.g. Cu In Se ₂ , Cu Ga Se ₂ , Cu In Ga Se ₂ }	<administrative transfer to H10F 77/126>
D	H01L 31/0323	6	{characterised by the doping material}	<administrative transfer to H10F 77/1265>
D	H01L 31/0324	5	{comprising only $A_{IV}B_{VI}$ or $A_{II}B_{IV}C_{VI}$ chalcogenide compounds, e.g. Pb Sn Te}	<administrative transfer to H10F 77/127>
D	H01L 31/0325	6	{characterised by the doping material}	<administrative transfer to H10F 77/1275>
D	H01L 31/0326	5	{comprising $A_{IV}B_{II}C_{IV}D_{VI}$ kesterite compounds, e.g. Cu ₂ ZnSnSe ₄ , Cu ₂ ZnSnS ₄ }	<administrative transfer to H10F 77/128>
D	H01L 31/0327	6	{characterised by the doping material}	<administrative transfer to H10F 77/1285>
D	H01L 31/0328	4	including, apart from doping materials or other impurities, semiconductor materials provided for in two or more of groups H01L 31/0272 - H01L 31/032	<administrative transfer to H10F 77/12>
D	H01L 31/0336	5	in different semiconductor regions, e.g. Cu ₂ X/CdX hetero-junctions, X being an element of Group VI of the Periodic Table	<administrative transfer to H10F 10/16>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/03365	6	{comprising only Cu_2X / CdX heterojunctions, X being an element of Group VI of the Periodic Table}	<administrative transfer to H10F 10/169>
D	H01L 2031/0344	3	{Organic materials}	<no transfer>
D	H01L 31/0352	2	characterised by their shape or by the shapes, relative sizes or disposition of the semiconductor regions	<administrative transfer to H10F 77/14>
D	H01L 31/035209	3	{comprising a quantum structures}	<administrative transfer to H10F 77/143>
D	H01L 31/035218	4	{the quantum structure being quantum dots}	<administrative transfer to H10F 77/1433>
D	H01L 31/035227	4	{the quantum structure being quantum wires, or nanorods (carbon nanotubes H10K 85/211)}	<administrative transfer to H10F 77/1437>
D	H01L 31/035236	3	{Superlattices; Multiple quantum well structures}	<administrative transfer to H10F 77/146>
D	H01L 31/035245	4	{characterised by amorphous semiconductor layers}	<administrative transfer to H10F 77/1462>
D	H01L 31/035254	4	{including, a part from doping materials or other impurities, only elements of Group IV of the Periodic Table, e.g. Si-SiGe superlattices}	<administrative transfer to H10F 77/1465>
D	H01L 31/035263	4	{Doping superlattices, e.g. nipi superlattices}	<administrative transfer to H10F 77/1468>
D	H01L 31/035272	3	{characterised by at least one potential jump barrier or surface barrier}	<administrative transfer to H10F 77/14>
D	H01L 31/035281	4	{Shape of the body}	<administrative transfer to H10F 77/147>
D	H01L 31/03529	4	{Shape of the potential jump barrier or surface barrier}	<administrative transfer to H10F 77/148>
D	H01L 31/036	2	characterised by their crystalline structure or particular orientation of the crystalline planes	<administrative transfer to H10F 77/16>
D	H01L 31/0368	3	including polycrystalline semiconductors (H01L 31/0392 takes precedence)	<administrative transfer to H10F 77/164>
D	H01L 31/03682	4	{including only elements of Group IV of the Periodic Table}	<administrative transfer to H10F 77/1642>
D	H01L 31/03685	5	{including microcrystalline silicon, uc-Si}	<administrative transfer to H10F 77/1645>
D	H01L 31/03687	5	{including microcrystalline $A_{IV}B_{IV}$ alloys, e.g. uc-SiGe, uc-SiC}	<administrative transfer to H10F 77/1648>
D	H01L 31/0376	3	including amorphous semiconductors (H01L 31/0392 takes precedence)	<administrative transfer to H10F 77/166>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/03762	4	{including only elements of Group IV of the Periodic Table}	<administrative transfer to H10F 77/1662>
D	H01L 31/03765	5	{including A _{IV} B _{IV} compounds or alloys, e.g. SiGe, SiC}	<administrative transfer to H10F 77/1665>
D	H01L 31/03767	5	{presenting light-induced characteristic variations, e.g. Staebler-Wronski effect}	<administrative transfer to H10F 77/1668>
D	H01L 31/0384	3	including other non-monocrystalline materials, e.g. semiconductor particles embedded in an insulating material (H01L 31/0392 takes precedence)	<administrative transfer to H10F 77/162>
D	H01L 31/03845	4	{comprising semiconductor nanoparticles embedded in a semiconductor matrix (in insulating matrix H01L 31/0384)}	<administrative transfer to H10F 77/1625>
D	H01L 31/0392	3	including thin films deposited on metallic or insulating substrates {; characterised by specific substrate materials or substrate features or by the presence of intermediate layers, e.g. barrier layers, on the substrate (textured substrates H01L 31/02366)}	<administrative transfer to H10F 77/169>
D	H01L 31/03921	4	{including only elements of Group IV of the Periodic Table}	<administrative transfer to H10F 77/1692>
D	H01L 31/03923	4	{including A _I B _{III} C _{VI} compound materials, e.g. CIS, CIGS}	<administrative transfer to H10F 77/1694>
D	H01L 31/03925	4	{including A _{II} B _{VI} compound materials, e.g. CdTe, CdS}	<administrative transfer to H10F 77/1696>
D	H01L 31/03926	4	{comprising a flexible substrate}	<administrative transfer to H10F 77/1698>
D	H01L 31/03928	5	{including A _I B _{III} C _{VI} compound, e.g. CIS, CIGS deposited on metal or polymer foils}	<administrative transfer to H10F 77/1699>
D	H01L 31/04	1	adapted as photovoltaic [PV] conversion devices (testing thereof during manufacture {H01L 22/00}; testing thereof after manufacture H02S 50/10)	<administrative transfer to H10F 10/00>
D	H01L 31/041	2	Provisions for preventing damage caused by corpuscular radiation, e.g. for space applications	<administrative transfer to H10F 77/80>
D	H01L 31/042	2	PV modules or arrays of single PV cells (supporting structures for PV modules H02S 20/00)	<administrative transfer to H10F 19/00>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/043	3	Mechanically stacked PV cells	<administrative transfer to H10F 19/40>
D	H01L 31/044	3	including bypass diodes (bypass diodes in the junction box H02S 40/34)	<administrative transfer to H10F 19/70>
D	H01L 31/0443	4	comprising bypass diodes integrated or directly associated with the devices, e.g. bypass diodes integrated or formed in or on the same substrate as the photovoltaic cells	<administrative transfer to H10F 19/75>
D	H01L 31/0445	3	including thin film solar cells, e.g. single thin film a-Si, CIS or CdTe solar cells	<administrative transfer to H10F 19/30>
D	H01L 31/046	4	PV modules composed of a plurality of thin film solar cells deposited on the same substrate	<administrative transfer to H10F 19/31>
D	H01L 31/0463	5	characterised by special patterning methods to connect the PV cells in a module, e.g. laser cutting of the conductive or active layers	<administrative transfer to H10F 19/33>
D	H01L 31/0465	5	comprising particular structures for the electrical interconnection of adjacent PV cells in the module (H01L 31/0463 takes precedence)	<administrative transfer to H10F 19/35>
D	H01L 31/0468	5	comprising specific means for obtaining partial light transmission through the module, e.g. partially transparent thin film solar modules for windows	<administrative transfer to H10F 19/37>
D	H01L 31/047	3	PV cell arrays including PV cells having multiple vertical junctions or multiple V-groove junctions formed in a semiconductor substrate	<administrative transfer to H10F 19/10>
D	H01L 31/0475	3	PV cell arrays made by cells in a planar, e.g. repetitive, configuration on a single semiconductor substrate; PV cell microarrays (PV modules composed of a plurality of thin film solar cells deposited on the same substrate H01L 31/046)	<administrative transfer to H10F 19/20>
D	H01L 31/048	3	Encapsulation of modules	<administrative transfer to H10F 19/80>
D	H01L 31/0481	4	{characterised by the composition of the encapsulation material}	<administrative transfer to H10F 19/804>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/0488	4	{Double glass encapsulation, e.g. photovoltaic cells arranged between front and rear glass sheets}	<administrative transfer to H10F 19/807>
D	H01L 31/049	4	Protective back sheets	<administrative transfer to H10F 19/85>
D	H01L 31/05	3	Electrical interconnection means between PV cells inside the PV module, e.g. series connection of PV cells (electrodes H01L 31/0224; electrical interconnection of thin film solar cells formed on a common substrate H01L 31/046; particular structures for electrical interconnecting of adjacent thin film solar cells in the module H01L 31/0465; electrical interconnection means specially adapted for electrically connecting two or more PV modules H02S 40/36)	<administrative transfer to H10F 19/90>
D	H01L 31/0504	4	{specially adapted for series or parallel connection of solar cells in a module}	<administrative transfer to H10F 19/902>
D	H01L 31/0508	5	{the interconnection means having a particular shape}	<administrative transfer to H10F 19/904>
D	H01L 31/0512	5	{made of a particular material or composition of materials}	<administrative transfer to H10F 19/906>
D	H01L 31/0516	5	{specially adapted for interconnection of back-contact solar cells}	<administrative transfer to H10F 19/908>
D	H01L 31/052	2	Cooling means directly associated or integrated with the PV cell, e.g. integrated Peltier elements for active cooling or heat sinks directly associated with the PV cells (cooling means in combination with the PV module H02S 40/42)	<administrative transfer to H10F 77/63>
D	H01L 31/0521	3	{using a gaseous or a liquid coolant, e.g. air flow ventilation, water circulation}	<administrative transfer to H10F 77/68>
D	H01L 31/0525	3	including means to utilise heat energy directly associated with the PV cell, e.g. integrated Seebeck elements	<administrative transfer to H10F 77/67>
D	H01L 31/053	2	Energy storage means directly associated or integrated with the PV cell, e.g. a capacitor integrated with a PV cell (energy storage means	<administrative transfer to H10F 77/90>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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			a associated with the PV module H02S 40/38)	
D	H01L 31/054	2	Optical elements directly associated or integrated with the PV cell, e.g. light-reflecting means or light-concentrating means	<administrative transfer to H10F 77/42>
D	H01L 31/0543	3	{comprising light concentrating means of the refractive type, e.g. lenses}	<administrative transfer to H10F 77/484>
D	H01L 31/0547	3	{comprising light concentrating means of the reflecting type, e.g. parabolic mirrors, concentrators using total internal reflection}	<administrative transfer to H10F 77/488>
D	H01L 31/0549	3	{comprising spectrum splitting means, e.g. dichroic mirrors}	<administrative transfer to H10F 77/492>
D	H01L 31/055	3	where light is absorbed and re-emitted at a different wavelength by the optical element directly associated or integrated with the PV cell, e.g. by using luminescent material, fluorescent concentrators or up-conversion arrangements	<administrative transfer to H10F 77/45>
D	H01L 31/056	3	the light-reflecting means being of the back surface reflector [BSR] type	<administrative transfer to H10F 77/48>
D	H01L 31/06	2	characterised by potential barriers	<administrative transfer to H10F 10/10>
D	H01L 31/061	3	the potential barriers being of the point-contact type (H01L 31/07 takes precedence)	<administrative transfer to H10F 10/11>
D	H01L 31/062	3	the potential barriers being only of the metal-insulator-semiconductor type	<administrative transfer to H10F 10/12>
D	H01L 31/065	3	the potential barriers being only of the graded gap type	<administrative transfer to H10F 10/13>
D	H01L 31/068	3	the potential barriers being only of the PN homojunction type, e.g. bulk silicon PN homojunction solar cells or thin film polycrystalline silicon PN homojunction solar cells	<administrative transfer to H10F 10/14>
D	H01L 31/0682	4	{back-junction, i.e. rearside emitter, solar cells, e.g. interdigitated base-emitter regions back-junction cells}	<administrative transfer to H10F 10/146>
D	H01L 31/0684	4	{double emitter cells, e.g. bifacial solar cells}	<administrative transfer to H10F 10/148>
D	H01L 31/0687	4	Multiple junction or tandem solar cells	<administrative transfer to H10F 10/142>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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D	H01L 31/06875	5	{inverted grown metamorphic [IMM] multiple junction solar cells, e.g. III-V compounds inverted metamorphic multi-junction cells}	<administrative transfer to H10F 10/1425>
D	H01L 31/0693	4	the devices including, apart from doping material or other impurities, only $A_{III}B_V$ compounds, e.g. GaAs or InP solar cells	<administrative transfer to H10F 10/144>
D	H01L 31/07	3	the potential barriers being only of the Schottky type	<administrative transfer to H10F 10/18>
D	H01L 31/072	3	the potential barriers being only of the PN heterojunction type	<administrative transfer to H10F 10/16>
D	H01L 31/0725	4	Multiple junction or tandem solar cells	<administrative transfer to H10F 10/161>
D	H01L 31/073	4	comprising only $A_{II}B_{VI}$ compound semiconductors, e.g. CdS/CdTe solar cells	<administrative transfer to H10F 10/162>
D	H01L 31/0735	4	comprising only $A_{III}B_V$ compound semiconductors, e.g. GaAs/AlGaAs or InP/GaInAs solar cells	<administrative transfer to H10F 10/163>
D	H01L 31/074	4	comprising a heterojunction with an element of Group IV of the Periodic Table, e.g. ITO/Si, GaAs/Si or CdTe/Si solar cells	<administrative transfer to H10F 10/164>
D	H01L 31/0745	4	comprising a $A_{IV}B_{IV}$ heterojunction, e.g. Si/Ge, SiGe/Si or Si/SiC solar cells	<administrative transfer to H10F 10/165>
D	H01L 31/0747	5	comprising a heterojunction of crystalline and amorphous materials, e.g. heterojunction with intrinsic thin layer	<administrative transfer to H10F 10/166>
D	H01L 31/0749	4	including a $A_I B_{III} C_{VI}$ compound, e.g. CdS/CuInSe ₂ [CIS] heterojunction solar cells	<administrative transfer to H10F 10/167>
D	H01L 31/075	3	the potential barriers being only of the PIN type, e.g. amorphous silicon PIN solar cells	<administrative transfer to H10F 10/17>
D	H01L 31/076	4	Multiple junction or tandem solar cells	<administrative transfer to H10F 10/172>
D	H01L 31/077	4	the devices comprising monocrystalline or polycrystalline materials	<administrative transfer to H10F 10/174>
D	H01L 31/078	3	including different types of potential barriers provided for in two or more of groups H01L 31/062 - H01L 31/075	<administrative transfer to H10F 10/19>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/08	1	in which radiation controls flow of current through the device, e.g. photoresistors	<administrative transfer to H10F 30/00>
D	H01L 31/085	2	{the device being sensitive to very short wavelength, e.g. X-ray, Gamma-rays}	<administrative transfer to H10F 30/301>
D	H01L 31/09	2	Devices sensitive to infrared, visible or ultra violet radiation (H01L 31/101 takes precedence)	<administrative transfer to H10F 30/10>
D	H01L 31/095	3	{comprising amorphous semiconductors}	<administrative transfer to H10F 30/15>
D	H01L 31/10	2	characterised by potential barriers, e.g. phototransistors	<administrative transfer to H10F 30/20>
D	H01L 31/101	3	Devices sensitive to infrared, visible or ultra violet radiation	<administrative transfer to H10F 30/21>
D	H01L 31/1013	4	{devices sensitive to two or more wavelengths, e.g. multi-spectrum radiation detection devices}	<administrative transfer to H10F 30/288>
D	H01L 31/1016	4	{comprising transparent or semitransparent devices}	<administrative transfer to H10F 30/289>
D	H01L 31/102	4	characterised by only one potential barrier	<administrative transfer to H10F 30/22>
D	H01L 31/1025	5	{the potential barrier being of the point contact type}	<administrative transfer to H10F 30/2205>
D	H01L 31/103	5	the potential barrier being of the PN homojunction type	<administrative transfer to H10F 30/221>
D	H01L 31/1032	6	{the devices comprising active layers formed only by A _{III} B _{VI} compounds, e.g. HgCdTe IR photodiodes}	<administrative transfer to H10F 30/2212>
D	H01L 31/1035	6	{the devices comprising active layers formed only by A _{III} B _V compounds}	<administrative transfer to H10F 30/2215>
D	H01L 31/1037	6	{the devices comprising active layers formed only by A _{IV} B _{VI} compounds}	<administrative transfer to H10F 30/2218>
D	H01L 31/105	5	the potential barrier being of the PIN type	<administrative transfer to H10F 30/223>
D	H01L 31/1055	6	{the devices comprising amorphous materials of Group IV of the Periodic Table}	<administrative transfer to H10F 30/2235>
D	H01L 31/107	5	the potential barrier working in a avalanche mode, e.g. a avalanche photodiodes	<administrative transfer to H10F 30/225>
D	H01L 31/1075	6	{in which the active layers, e.g. absorption or multiplication layers, form an heterostructure, e.g. SAM structure}	<administrative transfer to H10F 30/2255>
D	H01L 31/108	5	the potential barrier being of the Schottky type	<administrative transfer to H10F 30/227>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/1085	6	{the devices being of the Metal-Semiconductor-Metal [MSM] Schottky barrier type}	<administrative transfer to H10F 30/2275>
D	H01L 31/109	5	the potential barrier being of the PN heterojunction type	<administrative transfer to H10F 30/222>
D	H01L 31/11	4	characterised by two potential barriers, e.g. bipolar phototransistors	<administrative transfer to H10F 30/24>
D	H01L 31/1105	5	{the device being a bipolar phototransistor}	<administrative transfer to H10F 30/245>
D	H01L 31/111	4	characterised by at least three potential barriers, e.g. photothyristors	<administrative transfer to H10F 30/26>
D	H01L 31/1113	5	{the device being a photothyristor}	<administrative transfer to H10F 30/263>
D	H01L 31/1116	6	{of the static induction type}	<administrative transfer to H10F 30/2635>
D	H01L 31/112	4	characterised by field-effect operation, e.g. junction field-effect phototransistor	<administrative transfer to H10F 30/28>
D	H01L 31/1121	5	{Devices with Schottky gate}	<administrative transfer to H10F 30/283>
D	H01L 31/1122	6	{the device being a CCD device}	<administrative transfer to H10F 30/2837>
D	H01L 31/1123	6	{the device being a photoMESFET}	<administrative transfer to H10F 30/2843>
D	H01L 31/1124	5	{Devices with PN homojunction gate}	<administrative transfer to H10F 30/285>
D	H01L 31/1125	6	{the device being a CCD device}	<administrative transfer to H10F 30/2857>
D	H01L 31/1126	6	{the device being a field-effect phototransistor}	<administrative transfer to H10F 30/2863>
D	H01L 31/1127	5	{Devices with PN heterojunction gate}	<administrative transfer to H10F 30/287>
D	H01L 31/1128	6	{the device being a CCD device}	<administrative transfer to H10F 30/2873>
D	H01L 31/1129	6	{the device being a field-effect phototransistor}	<administrative transfer to H10F 30/2877>
D	H01L 31/113	5	being of the conductor-insulator-semiconductor type, e.g. metal-insulator-semiconductor field-effect transistor	<administrative transfer to H10F 30/2823>
D	H01L 31/1133	6	{the device being a conductor-insulator-semiconductor diode or a CCD device}	<administrative transfer to H10F 30/2823>
D	H01L 31/1136	6	{the device being a metal-insulator-semiconductor field-effect transistor}	<administrative transfer to H10F 30/282>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/115	3	Devices sensitive to very short wavelength, e.g. X-rays, gamma-rays or corpuscular radiation	<administrative transfer to H10F 30/29>
D	H01L 31/117	4	of the bulk effect radiation detector type, e.g. Ge-Li compensated PIN gamma-ray detectors	<administrative transfer to H10F 30/292>
D	H01L 31/1175	5	{Li compensated PIN gamma-ray detectors}	<administrative transfer to H10F 30/2925>
D	H01L 31/118	4	of the surface barrier or shallow PN junction detector type, e.g. surface barrier alpha-particle detectors	<administrative transfer to H10F 30/295>
D	H01L 31/1185	5	{of the shallow PN junction detector type}	<administrative transfer to H10F 30/2955>
D	H01L 31/119	4	characterised by field-effect operation, e.g. MIS type detectors	<administrative transfer to H10F 30/298>
D	H01L 31/12	1	structurally associated with, e.g. formed in or on a common substrate with, one or more electric light sources, e.g. electroluminescent light sources, and electrically or optically coupled thereto (semiconductor devices with at least one potential barrier or surface barrier adapted for light emission H01L 33/00; amplifiers using electroluminescent element and photocell H03F 17/00; electroluminescent light sources <u>per se</u> H05B 33/00)	<administrative transfer to H10F 55/00>
D	H01L 31/125	2	{Composite devices with photosensitive elements and electroluminescent elements within one single body}	<administrative transfer to H10F 55/18>
D	H01L 31/14	2	the light source or sources being controlled by the semiconductor device sensitive to radiation, e.g. image converters, image amplifiers or image storage devices	<administrative transfer to H10F 55/10>
D	H01L 31/141	3	{the semiconductor device sensitive to radiation being without a potential-jump barrier or surface barrier}	<administrative transfer to H10F 55/16>
D	H01L 31/143	4	{the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. light emitting diode}	<administrative transfer to H10F 55/165>
D	H01L 31/145	3	{the semiconductor device sensitive to radiation being characterised by at	<administrative transfer to H10F 55/17>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
			least one potential-jump barrier or surface barrier}	
D	H01L 31/147	3	the light sources and the devices sensitive to radiation all being semiconductor devices characterised by potential barriers	<administrative transfer to H10F 55/15>
D	H01L 31/153	4	formed in, or on, a common substrate	<administrative transfer to H10F 55/155>
D	H01L 31/16	2	the semiconductor device sensitive to radiation being controlled by the light source or sources	<administrative transfer to H10F 55/20>
D	H01L 31/161	3	{Semiconductor device sensitive to radiation without a potential-jump or surface barrier, e.g. photoresistors}	<administrative transfer to H10F 55/205>
D	H01L 31/162	4	{the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. a light emitting diode}	<administrative transfer to H10F 55/207>
D	H01L 31/164	4	{Optical potentiometers}	<administrative transfer to H10F 55/208>
D	H01L 31/165	3	{the semiconductor sensitive to radiation being characterised by at least one potential-jump or surface barrier}	<administrative transfer to H10F 55/26>
D	H01L 31/167	3	the light sources and the devices sensitive to radiation all being semiconductor devices characterised by potential barriers	<administrative transfer to H10F 55/25>
D	H01L 31/173	4	formed in, or on, a common substrate	<administrative transfer to H10F 55/255>
D	H01L 31/18	1	Processes or apparatus specially adapted for the manufacture or treatment of these devices or of parts thereof	<administrative transfer to H10F 71/00>
D	H01L 31/1804	2	{comprising only elements of Group IV of the Periodic Table}	<administrative transfer to H10F 71/121>
D	H01L 31/1808	3	{including only Ge}	<administrative transfer to H10F 71/1212>
D	H01L 31/1812	3	{including only A _{IV} B _{IV} alloys, e.g. SiGe}	<administrative transfer to H10F 71/1215>
D	H01L 31/1816	4	{Special manufacturing methods for microcrystalline layers, e.g. uc-SiGe, uc-SiC}	<administrative transfer to H10F 71/1218>
D	H01L 31/182	3	{Special manufacturing methods for polycrystalline Si, e.g. Si ribbon, poly Si ingots, thin films of polycrystalline Si}	<administrative transfer to H10F 71/1221>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/1824	4	{Special manufacturing methods for microcrystalline Si, uc-Si}	<administrative transfer to H10F 71/1224>
D	H01L 31/1828	2	{the active layers comprising only A _{II} B _{VI} compounds, e.g. CdS, ZnS, CdTe}	<administrative transfer to H10F 71/125>
D	H01L 31/1832	3	{comprising ternary compounds, e.g. HgCdTe}	<administrative transfer to H10F 71/1253>
D	H01L 31/1836	3	{comprising a growth substrate not being an A _{II} B _{VI} compound}	<administrative transfer to H10F 71/1257>
D	H01L 31/184	2	{the active layers comprising only A _{III} B _V compounds, e.g. GaAs, InP}	<administrative transfer to H10F 71/127>
D	H01L 31/1844	3	{comprising ternary or quaternary compounds, e.g. GaAlAs, InGaAsP}	<administrative transfer to H10F 71/1272>
D	H01L 31/1848	4	{comprising nitride compounds, e.g. InGaN, InGaAlN}	<administrative transfer to H10F 71/1274>
D	H01L 31/1852	3	{comprising a growth substrate not being an A _{III} B _V compound}	<administrative transfer to H10F 71/1276>
D	H01L 31/1856	3	{comprising nitride compounds, e.g. GaN}	<administrative transfer to H10F 71/1278>
D	H01L 31/186	2	{Particular post-treatment for the devices, e.g. annealing, impurity gettering, short-circuit elimination, recrystallisation}	<administrative transfer to H10F 71/00>
D	H01L 31/1864	3	{Annealing}	<administrative transfer to H10F 71/128>
D	H01L 31/1868	3	{Passivation}	<administrative transfer to H10F 71/129>
D	H01L 31/1872	3	{Recrystallisation}	<administrative transfer to H10F 71/131>
D	H01L 31/1876	2	{Particular processes or apparatus for batch treatment of the devices}	<administrative transfer to H10F 71/137>
D	H01L 31/188	3	{Apparatus specially adapted for automatic interconnection of solar cells in a module}	<administrative transfer to H10F 71/1375>
D	H01L 31/1884	2	{Manufacture of transparent electrodes, e.g. TCO, ITO}	<administrative transfer to H10F 71/138>
D	H01L 31/1888	3	{methods for etching transparent electrodes}	<administrative transfer to H10F 71/1385>
D	H01L 31/1892	2	{methods involving the use of temporary, removable substrates}	<administrative transfer to H10F 71/139>
D	H01L 31/1896	3	{for thin-film semiconductors}	<administrative transfer to H10F 71/1395>
D	H01L 31/20	2	such devices or parts thereof comprising amorphous semiconductor materials	<administrative transfer to H10F 71/10>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 31/202	3	{including only elements of Group IV of the Periodic Table}	<administrative transfer to H10F 71/103>
D	H01L 31/204	4	{including A _{IV} B _{IV} alloys, e.g. SiGe, SiC}	<administrative transfer to H10F 71/1035>
D	H01L 31/206	3	{Particular processes or apparatus for continuous treatment of the devices, e.g. roll-to roll processes, multi-chamber deposition}	<administrative transfer to H10F 71/107>
D	H01L 31/208	3	{Particular post-treatment of the devices, e.g. annealing, short-circuit elimination}	<administrative transfer to H10F 71/10>

SUBCLASS H10F - INORGANIC SEMICONDUCTOR DEVICES SENSITIVE TO INFRARED RADIATION, LIGHT, ELECTROMAGNETIC RADIATION OF SHORTER WAVELENGTH OR CORPUSCULAR RADIATION

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F	Subclass	INORGANIC SEMICONDUCTOR DEVICES SENSITIVE TO INFRARED RADIATION, LIGHT, ELECTROMAGNETIC RADIATION OF SHORTER WAVELENGTH OR CORPUSCULAR RADIATION	
N	H10F 10/00	0	Individual photovoltaic cells, e.g. solar cells (electrolytic light-sensitive devices, e.g. dye-sensitised solar cells, H01G9/20)	
N	H10F 10/10	1	having potential barriers	
N	H10F 10/11	2	Photovoltaic cells having point contact potential barriers (H10F 10/18 takes precedence)	
N	H10F 10/12	2	Photovoltaic cells having only metal-insulator-semiconductor [MIS] potential barriers	
N	H10F 10/13	2	Photovoltaic cells having absorbing layers comprising graded bandgaps	
N	H10F 10/14	2	Photovoltaic cells having only PN homojunction potential barriers	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 10/142	3	comprising multiple PN homojunctions, e.g. tandem cells	
N	H10F 10/1425	4	{Inverted metamorphic multi-junction [IMM] photovoltaic cells}	
N	H10F 10/144	3	comprising only Group III-V materials, e.g. GaAs, AlGaAs, or InP photovoltaic cells	
N	H10F 10/146	3	{Back-junction photovoltaic cells, e.g. having interdigitated base-emitter regions on the back side}	
N	H10F 10/148	3	{Double-emitter photovoltaic cells, e.g. bifacial photovoltaic cells}	
N	H10F 10/16	2	Photovoltaic cells having only PN heterojunction potential barriers	
N	H10F 10/161	3	comprising multiple PN heterojunctions, e.g. tandem cells	
N	H10F 10/162	3	comprising only Group II-VI materials, e.g. CdS/CdTe photovoltaic cells	
N	H10F 10/163	3	comprising only Group III-V materials, e.g. GaAs/AlGaAs or InP/GaInAs photovoltaic cells	
N	H10F 10/164	3	comprising heterojunctions with Group IV materials, e.g. ITO/Si or GaAs/SiGe photovoltaic cells	
N	H10F 10/165	4	the heterojunctions being Group IV-IV heterojunctions, e.g. Si/Ge, SiGe/Si or Si/SiC photovoltaic cells	
N	H10F 10/166	5	the Group IV-IV heterojunctions being heterojunctions of crystalline and amorphous materials, e.g. silicon heterojunction [SHJ] photovoltaic cells	
N	H10F 10/167	3	comprising Group I-III-VI materials, e.g. CdS/CuInSe ₂ [CIS] heterojunction photovoltaic cells	
N	H10F 10/169	3	{comprising Cu ₂ X/CdX heterojunctions, wherein X is a Group VI element, e.g. Cu ₂ O/CdO PN heterojunction photovoltaic cells}	
N	H10F 10/17	2	Photovoltaic cells having only PIN junction potential barriers	
N	H10F 10/172	3	comprising multiple PIN junctions, e.g. tandem cells	
N	H10F 10/174	3	comprising monocrystalline or polycrystalline materials	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 10/18	2	Photovoltaic cells having only Schottky potential barriers	
N	H10F 10/19	2	Photovoltaic cells having multiple potential barriers of different types, e.g. tandem cells having both PN and PIN junctions	
N	H10F 19/00	0	Integrated devices, or assemblies of multiple devices, comprising at least one photovoltaic cell covered by group H10F 10/00, e.g. photovoltaic modules	
N	H10F 19/10	1	comprising photovoltaic cells in arrays in a single semiconductor substrate, the photovoltaic cells having vertical junctions or V-groove junctions	
N	H10F 19/20	1	comprising photovoltaic cells in arrays in or on a single semiconductor substrate, the photovoltaic cells having planar junctions (having multiple thin-film photovoltaic cells deposited on the same substrate H10F 19/31)	
N	H10F 19/30	1	comprising thin-film photovoltaic cells	
N	H10F 19/31	2	having multiple laterally adjacent thin-film photovoltaic cells deposited on the same substrate	
N	H10F 19/33	3	Patterning processes to connect the photovoltaic cells, e.g. laser cutting of conductive or active layers	
N	H10F 19/35	3	Structures for the connecting of adjacent photovoltaic cells, e.g. interconnections or insulating spacers	
N	H10F 19/37	3	comprising means for obtaining partial light transmission through the integrated devices, or the assemblies of multiple devices, e.g. partially transparent thin-film photovoltaic modules for windows	
N	H10F 19/40	1	comprising photovoltaic cells in a mechanically stacked configuration	
N	H10F 19/50	1	Integrated devices comprising at least one photovoltaic cell and other types of semiconductor or solid-state	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
			components (H10F 19/75 takes precedence)	
N	H10F 19/70	1	comprising bypass diodes (bypass diodes in a junction box H02S 40/34)	
N	H10F 19/75	2	the bypass diodes being integrated or directly associated with the photovoltaic cells, e.g. formed in or on the same substrate	
N	H10F 19/80	1	Encapsulations or containers for integrated devices, or assemblies of multiple devices, having photovoltaic cells	
N	H10F 19/804	2	{Materials of encapsulations}	
N	H10F 19/807	2	{Double-glass encapsulation, e.g. photovoltaic cells arranged between front and rear glass sheets}	
N	H10F 19/85	2	Protective back sheets	
N	H10F 19/90	1	Structures for connecting between photovoltaic cells, e.g. interconnections or insulating spacers (between thin-film photovoltaic cells on a single substrate H10F 19/35)	
N	H10F 19/902	2	{for series or parallel connection of photovoltaic cells}	
N	H10F 19/904	3	{characterised by the shapes of the structures}	
N	H10F 19/906	3	{characterised by the materials of the structures}	
N	H10F 19/908	3	{for back-contact photovoltaic cells}	
N	H10F 30/00	0	Individual radiation-sensitive semiconductor devices in which radiation controls the flow of current through the devices, e.g. photodetectors	
N	H10F 30/10	1	the devices being sensitive to infrared radiation, visible or ultra violet radiation, and having no potential barriers, e.g. photoresistors	
N	H10F 30/15	2	{comprising amorphous semiconductors}	
N	H10F 30/20	1	the devices having potential barriers, e.g. phototransistors	
N	H10F 30/21	2	the devices being sensitive to infrared, visible or ultra violet radiation	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	Transferred to#
N	H10F 30/22	3	the devices having only one potential barrier, e.g. photodiodes	
N	H10F 30/2205	4	{the potential barrier being a point contact}	
N	H10F 30/221	4	the potential barrier being a PN homojunction	
N	H10F 30/2212	5	{the devices comprising active layers made of only Group II-VI materials, e.g. HgCdTe infrared photodiodes}	
N	H10F 30/2215	5	{the devices comprising active layers made of only Group III-V materials}	
N	H10F 30/2218	5	{the devices comprising active layers made of only Group IV-VI materials}	
N	H10F 30/222	4	the potential barrier being a PN heterojunction	
N	H10F 30/223	4	the potential barrier being a PIN barrier	
N	H10F 30/2235	5	{the devices comprising Group IV amorphous materials}	
N	H10F 30/225	4	the potential barrier working in a avalanche mode, e.g. avalanche photodiodes	
N	H10F 30/2255	5	{in which the active layers form heterostructures, e.g. SAM structures}	
N	H10F 30/227	4	the potential barrier being a Schottky barrier	
N	H10F 30/2275	5	{being a metal-semiconductor-metal [MSM] Schottky barrier}	
N	H10F 30/24	3	the devices having only two potential barriers, e.g. bipolar phototransistors	
N	H10F 30/245	4	{Bipolar phototransistors}	
N	H10F 30/26	3	the devices having three or more potential barriers, e.g. photothyristors	
N	H10F 30/263	4	{Photothyristors}	
N	H10F 30/2635	5	{Static induction photothyristors}	
N	H10F 30/28	3	the devices being characterised by field-effect operation, e.g. junction field-effect phototransistors	
N	H10F 30/282	4	Insulated-gate field-effect transistors [IGFET], e.g. MISFET [metal-insulator-semiconductor field-effect transistor] phototransistors	
N	H10F 30/2823	4	{the devices being conductor-insulator-semiconductor devices, e.g. diodes or charge-coupled devices}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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			[CCD] (Insulated-gate field-effect transistors H10F 30/282)}	
N	H10F 30/283	4	{the devices having Schottky gates}	
N	H10F 30/2837	5	{CCDs having Schottky gates}	
N	H10F 30/2843	5	{Schottky gate FETs, e.g. photo MESFETs}	
N	H10F 30/285	4	{the devices having PN homojunction gates}	
N	H10F 30/2857	5	{CCDs having PN homojunction gates}	
N	H10F 30/2863	5	{Field-effect phototransistors having PN homojunction gates}	
N	H10F 30/287	4	{the devices having PN heterojunction gates}	
N	H10F 30/2873	5	{CCDs having PN heterojunction gates}	
N	H10F 30/2877	5	{Field-effect phototransistors having PN heterojunction gates}	
N	H10F 30/288	3	{the devices being sensitive to multiple wavelengths, e.g. multi-spectrum radiation detection devices}	
N	H10F 30/289	3	{the devices being transparent or semi-transparent devices}	
N	H10F 30/29	2	the devices being sensitive to radiation having very short wavelengths, e.g. X-rays, gamma-rays or corpuscular radiation	
N	H10F 30/292	3	Bulk-effect radiation detectors, e.g. Ge-Li compensated PIN gamma-ray detectors	
N	H10F 30/2925	4	{Li-compensated PIN gamma-ray detectors}	
N	H10F 30/295	3	Surface barrier or shallow PN junction radiation detectors, e.g. surface barrier alpha-particle detectors	
N	H10F 30/2955	4	{Shallow PN junction radiation detectors}	
N	H10F 30/298	3	the devices being characterised by field-effect operation, e.g. MIS type detectors	
N	H10F 30/301	1	{the devices being sensitive to very short wavelength, e.g. being sensitive to X-rays, gamma-rays or corpuscular radiation}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

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N	H10F 39/00	0	Integrated devices, or assemblies of multiple devices, comprising at least one element covered by group H10F 30/00, e.g. radiation detectors comprising photodiode arrays	
N	H10F 39/011	1	{Manufacture or treatment of image sensors covered by group H10F 39/12}	
N	H10F 39/014	2	{of CMOS image sensors}	
N	H10F 39/016	2	{of thin-film-based image sensors}	
N	H10F 39/018	2	{of hybrid image sensors}	
N	H10F 39/021	2	{of image sensors having active layers comprising only Group III-V materials, e.g. GaAs, AlGaAs or InP}	
N	H10F 39/022	2	{of image sensors having active layers comprising only Group II-VI materials, e.g. CdS, ZnS or CdTe}	
N	H10F 39/024	2	{of coatings or optical elements}	
N	H10F 39/026	2	{Wafer-level processing}	
N	H10F 39/028	2	{performed after manufacture of the image sensors, e.g. annealing, gettering of impurities, short-circuit elimination or recrystallisation}	
N	H10F 39/10	1	Integrated devices	
N	H10F 39/103	2	{the at least one element covered by H10F 30/00 having potential barriers, e.g. integrated devices comprising photodiodes or phototransistors}	
N	H10F 39/107	2	{having multiple elements covered by H10F 30/00 in a repetitive configuration, e.g. radiation detectors comprising photodiode arrays}	
N	H10F 39/12	2	Image sensors	
N	H10F 39/15	3	Charge-coupled device [CCD] image sensors	
N	H10F 39/151	4	{Geometry or disposition of pixel elements, address lines or gate electrodes}	
N	H10F 39/1515	5	{Optical shielding}	
N	H10F 39/152	4	{One-dimensional array CCD image sensors}	
N	H10F 39/153	4	{Two-dimensional or three-dimensional array CCD image sensors}	
N	H10F 39/1532	5	{Frame-interline transfer}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 39/1534	5	{Interline transfer}	
N	H10F 39/1536	5	{Frame transfer}	
N	H10F 39/1538	5	{Time-delay and integration}	
N	H10F 39/154	4	{Charge-injection device [CID] image sensors (H10F 39/156, H10F 39/157 take precedence)}	
N	H10F 39/156	4	{CCD or CID colour image sensors}	
N	H10F 39/157	4	{CCD or CID infrared image sensors}	
N	H10F 39/1575	5	{of the hybrid type}	
N	H10F 39/158	4	{having arrangements for blooming suppression}	
N	H10F 39/159	4	{comprising a photoconductive layer deposited on the CCD structure}	
N	H10F 39/18	3	Complementary metal-oxide-semiconductor [CMOS] image sensors; Photodiode array image sensors	
N	H10F 39/182	4	{Colour image sensors}	
N	H10F 39/1825	5	{Multicolour image sensors having stacked structure, e.g. NPN, NPNN or multiple quantum well [MQW] structures}	
N	H10F 39/184	4	{Infrared image sensors}	
N	H10F 39/1843	5	{of the hybrid type}	
N	H10F 39/1847	5	{Multispectral infrared image sensors having a stacked structure, e.g. NPN, NPNN or multiple quantum well [MQW] structures}	
N	H10F 39/186	4	{having arrangements for blooming suppression}	
N	H10F 39/1865	5	{Overflow drain structures}	
N	H10F 39/189	4	{X-ray, gamma-ray or corpuscular radiation imagers}	
N	H10F 39/1892	5	{Direct radiation image sensors}	
N	H10F 39/1895	5	{of the hybrid type}	
N	H10F 39/1898	5	{Indirect radiation image sensors, e.g. using luminescent members}	
N	H10F 39/191	3	{Photoconductor image sensors}	
N	H10F 39/192	4	{Colour image sensors}	
N	H10F 39/193	4	{Infrared image sensors}	
N	H10F 39/1935	5	{of the hybrid type}	
N	H10F 39/194	4	{having arrangements for blooming suppression}	
N	H10F 39/1945	5	{Overflow drain structures}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 39/195	4	{X-ray, gamma-ray or corpuscular radiation imagers}	
N	H10F 39/196	3	{Junction field effect transistor [JFET] image sensors; Static induction transistor [SIT] image sensors}	
N	H10F 39/197	3	{Bipolar transistor image sensors}	
N	H10F 39/198	3	{Contact-type image sensors [CIS]}	
N	H10F 39/199	3	{Back-illuminated image sensors}	
Q	H10F 39/80	1	{Constructional details of image sensors}	H10F 39/80, H10F 39/802, H10F 39/8023, H10F 39/8027, H10F 39/803, H10F 39/8033, H10F 39/8037, H10F 39/80373, H10F 39/80377, H10F 39/804, H10F 39/805, H10F 39/8053, H10F 39/8057, H10F 39/806, H10F 39/8063, H10F 39/8067, H10F 39/807, H10F39/809, H10F 39/811, H10F 39/812, H10F 39/813
N	H10F 39/802	2	{Geometry or disposition of elements in pixels, e.g. address-lines or gate electrodes}	
N	H10F 39/8023	3	{Disposition of the elements in pixels, e.g. smaller elements in the centre of the imager compared to larger elements at the periphery}	
N	H10F 39/8027	3	{Geometry of the photosensitive area}	
N	H10F 39/803	2	{Pixels having integrated switching, control, storage or amplification elements}	
N	H10F 39/8033	3	{Photosensitive area}	
N	H10F 39/8037	3	{the integrated elements comprising a transistor}	
N	H10F 39/80373	4	{characterised by the gate of the transistor}	
N	H10F 39/80377	4	{characterised by the channel of the transistor, e.g. channel having a doping gradient}	
N	H10F 39/804	2	{Containers or encapsulations}	
N	H10F 39/805	2	{Coatings}	
N	H10F 39/8053	3	{Colour filters}	
N	H10F 39/8057	3	{Optical shielding}	
N	H10F 39/806	2	{Optical elements or arrangements associated with the image sensors}	
N	H10F 39/8063	3	{Microlenses}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 39/8067	3	{Reflectors}	
N	H10F 39/807	2	{Pixel isolation structures}	
N	H10F39/809	2	{of hybrid image sensors}	
N	H10F 39/811	2	{Interconnections}	
N	H10F 39/812	2	{Arrangements for transferring the charges in the image sensor perpendicular to the imaging plane, e.g. buried regions used to transfer generated charges to circuitry under the photosensitive region}	
N	H10F 39/813	2	{Electronic components shared by multiple pixels, e.g. one amplifier shared by two pixels}	
N	H10F 39/90	1	Assemblies of multiple devices	
N	H10F 39/95	2	comprising at least one integrated device covered by group H10F 39/10, e.g. comprising integrated image sensors	
N	H10F 55/00	0	Radiation-sensitive semiconductor devices covered by groups H10F 10/00, H10F 19/00 or H10F 30/00 being structurally associated with electric light sources and electrically or optically coupled thereto	
N	H10F 55/10	1	wherein the radiation-sensitive semiconductor devices control the electric light source, e.g. image converters, image amplifiers or image storage devices	
N	H10F 55/15	2	wherein the radiation-sensitive devices and the electric light source are all semiconductor devices	
N	H10F55/155	3	formed in, or on, a common substrate	
N	H10F 55/16	2	{wherein the radiation-sensitive semiconductor devices have no potential barriers}	
N	H10F 55/165	3	{wherein the electric light source comprises semiconductor devices having potential barriers, e.g. light emitting diodes}	
N	H10F 55/17	2	{wherein the radiation-sensitive semiconductor devices have potential barriers}	
N	H10F 55/18	1	{wherein the radiation-sensitive semiconductor devices and the electric light source share a common	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
			body having dual-functionality of light emission and light detection }	
N	H10F 55/20	1	wherein the electric light source controls the radiation-sensitive semiconductor devices, e.g. optocouplers	
N	H10F 55/205	2	{wherein the radiation-sensitive semiconductor devices have no potential barriers, e.g. photoresistors }	
N	H10F 55/207	3	{wherein the electric light source comprises semiconductor devices having potential barriers, e.g. light emitting diodes }	
N	H10F 55/208	3	{Optical potentiometers }	
N	H10F 55/25	2	wherein the radiation-sensitive devices and the electric light source are all semiconductor devices	
N	H10F 55/255	3	formed in, or on, a common substrate	
N	H10F 55/26	2	{wherein the radiation-sensitive semiconductor devices have potential barriers }	
Q	H10F 71/00	0	Manufacture or treatment of devices covered by this subclass (patterning processes to connect thin photovoltaic cells in integrated devices, or assemblies of multiple devices, having photovoltaic cells H10F19/33; manufacture or treatment of encapsulations or containers for integrated devices, or assemblies of multiple devices, having photovoltaic cells H10F19/80; manufacture or treatment of integrated devices, or assemblies of multiple devices, comprising at least one element in which radiation controls the flow of current H10F39/00)	H10F 71/00, H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/135, H10F 71/136
Q	H10F 71/10	1	the devices comprising a morphous semiconductor material	H10F 71/10, H10F 71/103, H10F 71/1035, H10F 71/107, H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/136, H10F 71/135, H10F 71/137, H10F 71/1375, H10F

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
				71/138, H10F 71/1385, H10F 71/139, H10F 71/1395
N	H10F 71/103	2	{including only Group IV materials}	
N	H10F 71/1035	3	{having multiple Group IV elements, e.g. SiGe or SiC}	
N	H10F 71/107	2	{Continuous treatment of the devices, e.g. roll-to-roll processes or multi-chamber deposition}	
N	H10F 71/121	1	{The active layers comprising only Group IV materials}	
N	H10F 71/1212	2	{consisting of germanium}	
N	H10F 71/1215	2	{comprising at least two Group IV elements, e.g. SiGe}	
N	H10F 71/1218	3	{in microcrystalline form}	
N	H10F 71/1221	2	{comprising polycrystalline silicon}	
N	H10F 71/1224	2	{comprising microcrystalline silicon}	
N	H10F 71/125	1	{The active layers comprising only Group II-VI materials, e.g. CdS, ZnS or CdTe}	
N	H10F 71/1253	2	{comprising at least three elements, e.g. HgCdTe}	
N	H10F 71/1257	2	{comprising growth substrates not made of Group II-VI materials}	
N	H10F 71/127	1	{The active layers comprising only Group III-V materials, e.g. GaAs or InP}	
N	H10F 71/1272	2	{comprising at least three elements, e.g. GaAlAs or InGaAsP}	
N	H10F 71/1274	3	{comprising nitrides, e.g. InGaN or InGaAlN}	
N	H10F 71/1276	2	{comprising growth substrates not made of Group III-V materials}	
N	H10F 71/1278	2	{comprising nitrides, e.g. GaN}	
N	H10F 71/128	1	{Annealing}	
N	H10F 71/129	1	{Passivating}	
N	H10F 71/131	1	{Recrystallisation; Crystallization of amorphous or microcrystalline semiconductors}	
N	H10F 71/132	1	{Gettering}	
N	H10F 71/133	1	{Providing edge isolation}	
N	H10F 71/134	1	{Irradiation with electromagnetic or particle radiation}	
N	H10F 71/135	1	{Application of a bias; Current injection}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 71/136	1	{Singulating, e.g. dicing}	
N	H10F 71/137	1	{Batch treatment of the devices}	
N	H10F 71/1375	2	{Apparatus for automatic interconnection of photovoltaic cells in a module}	
N	H10F 71/138	1	{Manufacture of transparent electrodes, e.g. transparent conductive oxides [TCO] or indium tin oxide [ITO] electrodes}	
N	H10F 71/1385	2	{Etching transparent electrodes}	
N	H10F 71/139	1	{using temporary substrates}	
N	H10F 71/1395	2	{for thin-film devices}	
N	H10F 77/00	0	Constructional details of devices covered by this subclass (constructional details of integrated devices, or assemblies of multiple devices, comprising at least one element in which radiation controls the flow of current H10F 39/00)	
N	H10F 77/10	1	Semiconductor bodies	
N	H10F 77/12	2	Active materials	
N	H10F 77/121	3	comprising only selenium or only tellurium	
N	H10F 77/1215	4	{characterised by the dopants}	
N	H10F 77/122	3	comprising only Group IV materials	
N	H10F 77/1223	4	characterised by the dopants	
N	H10F 77/1226	4	comprising multiple Group IV elements, e.g. SiC	
N	H10F 77/1227	5	{characterised by the dopants}	
N	H10F 77/1228	4	{porous silicon}	
N	H10F 77/123	3	comprising only Group II-VI materials, e.g. CdS, ZnS or HgCdTe	
N	H10F 77/1233	4	{characterised by the dopants}	
N	H10F 77/1237	4	{having at least three elements, e.g. HgCdTe}	
N	H10F 77/124	3	comprising only Group III-V materials, e.g. GaAs	
N	H10F 77/1243	4	{characterised by the dopants}	
N	H10F 77/1246	4	{III-V nitrides, e.g. GaN}	
N	H10F 77/1248	4	{having three or more elements, e.g. GaAlAs, InGaAs or InGaAsP}	
N	H10F 77/12485	5	{comprising nitride compounds, e.g. InGaN}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 77/126	3	{comprising only Group I-III-VI chalcopyrite materials, e.g. CuInSe ₂ , CuGaSe ₂ or CuInGaSe ₂ [CIGS]}	
N	H10F 77/1265	4	{characterised by the dopants}	
N	H10F 77/127	3	{comprising only Group IV-VI or only Group II-IV-VI chalcogenide materials, e.g. PbSnTe}	
N	H10F 77/1275	4	{characterised by the dopants}	
N	H10F 77/128	3	{comprising only Group I-II-IV-VI kesterite materials, e.g. Cu ₂ ZnSnSe ₄ or Cu ₂ ZnSnS ₄ }	
N	H10F 77/1285	4	{characterised by the dopants}	
N	H10F 77/14	2	Shape of semiconductor bodies; Shapes, relative sizes or dispositions of semiconductor regions within semiconductor bodies	
N	H10F 77/143	3	{comprising quantum structures}	
N	H10F 77/1433	4	{Quantum dots}	
N	H10F 77/1437	4	{Quantum wires or nanorods}	
N	H10F 77/146	3	{Superlattices; Multiple quantum well structures}	
N	H10F 77/1462	4	{comprising amorphous semiconductor layers}	
N	H10F 77/1465	4	{including only Group IV materials, e.g. Si-SiGe superlattices}	
N	H10F 77/1468	4	{Doped superlattices, e.g. N-I-P-I superlattices}	
N	H10F 77/147	3	{Shapes of bodies}	
N	H10F 77/148	3	{Shapes of potential barriers}	
N	H10F 77/16	2	Material structures, e.g. crystalline structures, film structures or crystal plane orientations	
N	H10F 77/162	3	Non-monocrystalline materials, e.g. semiconductor particles embedded in insulating materials (H10F 77/169 takes precedence)	
N	H10F 77/1625	4	{Semiconductor nanoparticles embedded in semiconductor matrix}	
N	H10F 77/164	4	Polycrystalline semiconductors	
N	H10F 77/1642	5	{including only Group IV materials}	
N	H10F 77/1645	6	{including microcrystalline silicon}	
N	H10F 77/1648	6	{including microcrystalline Group IV-IV materials, e.g. microcrystalline SiGe}	
N	H10F 77/166	4	Amorphous semiconductors	
N	H10F 77/1662	5	{including only Group IV materials}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10F 77/1665	6	{including Group IV-IV materials, e.g. SiGe or SiC}	
N	H10F 77/1668	6	{presenting light-induced characteristic variations, e.g. Staebler-Wronski effect}	
N	H10F 77/169	3	Thin semiconductor films on metallic or insulating substrates	
N	H10F 77/1692	4	{the films including only Group IV materials}	
N	H10F 77/1694	4	{the films including Group I-III-VI materials, e.g. CIS or CIGS}	
N	H10F 77/1696	4	{the films including Group II-VI materials, e.g. CdTe or CdS}	
N	H10F 77/1698	4	{the metallic or insulating substrates being flexible}	
N	H10F 77/1699	5	{the films including Group I-III-VI materials, e.g. CIS or CIGS on metal foils or polymer foils}	
N	H10F 77/20	1	Electrodes	
N	H10F 77/206	2	{for devices having potential barriers}	
N	H10F 77/211	3	{for photovoltaic cells}	
N	H10F 77/215	4	{Geometries of grid contacts}	
N	H10F 77/219	4	{Arrangements for electrodes of back-contact photovoltaic cells}	
N	H10F 77/223	5	{for metallisation wrap-through [MWT] photovoltaic cells}	
N	H10F 77/227	5	{for emitter wrap-through [EWT] photovoltaic cells, e.g. interdigitated emitter-base back-contacts}	
N	H10F 77/241	3	{comprising ring electrodes}	
N	H10F 77/244	2	{made of transparent conductive layers, e.g. transparent conductive oxide [TCO] layers}	
N	H10F 77/247	3	{comprising indium tin oxide [ITO]}	
N	H10F 77/251	3	{comprising zinc oxide [ZnO]}	
N	H10F 77/254	3	{comprising a metal, e.g. transparent gold}	
N	H10F 77/30	1	Coatings (arrangements for preventing damage to photovoltaic cells caused by corpuscular radiation H10F 77/80)	
N	H10F 77/306	2	{for devices having potential barriers}	
N	H10F 77/311	3	{for photovoltaic cells}	
N	H10F 77/315	4	{the coatings being antireflective or having enhancing optical properties}	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Type*</u>	<u>Symbol</u>	<u>Indent Level Number of dots (e.g. 0, 1, 2)</u>	<u>Title</u> <u>“CPC only” text should normally be enclosed in {curly brackets}**</u>	<u>Transferred to#</u>
N	H10F 77/331	3	{for filtering or shielding light, e.g. multicolour filters for photodetectors}	
N	H10F 77/334	4	{for shielding light, e.g. light blocking layers or cold shields for infrared detectors}	
N	H10F 77/337	4	{using interference filters, e.g. multilayer dielectric filters}	
N	H10F 77/40	1	Optical elements or arrangements (surface textures H10F 77/70)	
N	H10F 77/407	2	{indirectly associated with the devices}	
N	H10F 77/413	2	{directly associated or integrated with the devices, e.g. back reflectors (directly associated or integrated with photovoltaic cells H10F 77/42)}	
N	H10F 77/42	2	directly associated or integrated with photovoltaic cells, e.g. light-reflecting means or light-concentrating means	
N	H10F 77/45	3	Wavelength conversion means, e.g. by using luminescent material, fluorescent concentrators or up-conversion arrangements	
N	H10F 77/48	3	Back surface reflectors [BSR]	
N	H10F 77/484	3	{Refractive light-concentrating means, e.g. lenses}	
N	H10F 77/488	3	{Reflecting light-concentrating means, e.g. parabolic mirrors or concentrators using total internal reflection}	
N	H10F 77/492	3	{Spectrum-splitting means, e.g. dichroic mirrors}	
N	H10F 77/496	2	{Luminescent members, e.g. fluorescent sheets (wavelength conversion means for photovoltaic cells H10F 77/45)}	
N	H10F 77/50	1	Encapsulations or containers (for photovoltaic modules H10F 19/80)	
N	H10F 77/60	1	Arrangements for cooling, heating, ventilating or compensating for temperature fluctuations	
N	H10F 77/63	2	Arrangements for cooling directly associated or integrated with photovoltaic cells, e.g. heat sinks directly associated with the	

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title “CPC only” text should normally be enclosed in {curly brackets}**	Transferred to#
			photovoltaic cells or integrated Peltier elements for active cooling	
N	H10F 77/67	3	including means to utilise heat energy directly associated with the photovoltaic cells, e.g. integrated Seebeck elements	
N	H10F 77/68	3	{using gaseous or liquid coolants, e.g. air flow ventilation or water circulation}	
N	H10F 77/70	1	Surface textures, e.g. pyramid structures	
N	H10F 77/703	2	{of the semiconductor bodies, e.g. textured active layers}	
N	H10F 77/707	2	{of the substrates or of layers on substrates, e.g. textured ITO layer on a glass substrate}	
N	H10F 77/80	1	Arrangements for preventing damage to photovoltaic cells caused by corpuscular radiation, e.g. for space applications	
N	H10F 77/90	1	Energy storage means directly associated or integrated with photovoltaic cells, e.g. capacitors integrated with photovoltaic cells	
N	H10F 77/93	1	{Interconnections}	
N	H10F 77/933	2	{for devices having potential barriers}	
N	H10F 77/935	3	{for photovoltaic devices or modules}	
N	H10F 77/937	4	{Busbar structures for modules}	
N	H10F 77/939	4	{Output lead wires or elements}	
N	H10F 77/95	1	{Circuit arrangements}	
N	H10F 77/953	2	{for devices having potential barriers}	
N	H10F 77/955	3	{for photovoltaic devices}	
N	H10F 77/957	3	{for position-sensitive photodetectors, e.g. lateral-effect photodiodes or quadrant photodiodes}	
N	H10F 77/959	3	{for devices working in a avalanche mode}	
Q	H10F 99/00	0	Subject matter not provided for in other groups of this subclass	H10F 99/00, H10F10/00, H10F 19/00, H10F30/00, H10F39/00, H10F 39/10

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

*N = new entries where reclassification into entries is involved; C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; T = existing entries with enlarged file scope, which receive documents from C or D entries, e.g. when a limiting reference is removed from the entry title; M = entries with no change to the file scope (no reclassification); D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed; U = entries that are unchanged.

NOTES:

- **No {curly brackets} are used for titles in CPC only subclasses, e.g. C12Y, A23Y; 2000 series symbol titles of groups found at the end of schemes (orthogonal codes); or the Y section titles. The {curly brackets} are used for 2000 series symbol titles found interspersed throughout the main trunk schemes (breakdown codes).
- U groups: it is obligatory to display the required “anchor” symbol (U group), i.e. the entry immediately preceding a new group or an array of new groups to be created (in case new groups are not clearly subgroups of C-type groups). Always include the symbol, indent level and title of the U group in the table above.
- All entry types should be included in the scheme changes table above for better understanding of the overall scheme change picture. Symbol, indent level, and title are required for all types.
- “Transferred to” column must be completed for all C, D, F, and Q type entries. F groups will be deleted once reclassification is completed.
- When multiple symbols are included in the “Transferred to” column, avoid using ranges of symbols in order to be as precise as possible.
- For administrative transfer of documents, the following text should be used: “<administrative transfer to XX>”, “<administrative transfer to XX and YY simultaneously>”, or “<administrative transfer to XX, YY, ...and ZZ simultaneously>” when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be “additional information”.
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations “ADD” or “INV”: <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or <administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the “D” entries of 2000-series or Y-series groups may not require a destination (“Transferred to”) symbol, however it is required to specify “<no transfer>” in the “Transferred to” column for such cases.
- For finalisation projects, the deleted “F” symbols should have <no transfer> in the “Transferred to” column.
- For more details about the types of schemes change, see CPC Guide.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

B. New, Modified or Deleted Warning(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
M	H01L	<p>1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups: H01L 21/203 covered by H01L 21/02631 H01L 21/205 covered by H01L 21/0262 H01L 21/208 covered by H01L 21/02623 H01L 21/301 covered by H01L 21/30 H01L 21/36 - H01L 21/368 covered by H01L 21/02107 H01L 21/58 covered by H01L 24/80 H01L 21/66 covered by H01L 22/00 H01L 21/98 covered by H01L 25/50</p> <p>2. {In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.}</p>	<p><u>Insert</u> the following new Warning after existing Warnings 1 and 2:</p> <p>3. Due to the ongoing developments in class H10 and related subclasses, the information displayed in notes, references and definitions of this subclass may not be entirely accurate. For each specific subject matter referred to in this subclass, users are invited to consult the relevant place in class H10 and to consider the class H10 information as correct, in case of conflict.</p>

SUBCLASS H10F - INORGANIC SEMICONDUCTOR DEVICES SENSITIVE TO INFRARED RADIATION, LIGHT, ELECTROMAGNETIC RADIATION OF SHORTER WAVELENGTH OR CORPUSCULAR RADIATION

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10F10/00		Group H10F 10/00 is incomplete pending reclassification of documents from group H10F 99/00. Groups H10F 99/00 and H10F 10/00 should be considered in order to perform a complete search.
N	H10F19/00		Group H10F 19/00 is incomplete pending reclassification of documents from group H10F 99/00. Groups H10F 99/00 and H10F 19/00 should be considered in order to perform a complete search.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10F30/00		Group H10F 30/00 is incomplete pending reclassification of documents from group H10F 99/00. Groups H10F 99/00 and H10F 30/00 should be considered in order to perform a complete search.
N	H10F39/00		Groups H10F 39/00 and H10F 39/10 are incomplete pending reclassification of documents from group H10F 99/00. Groups H10F 99/00, H10F 39/00 and H10F 39/10 should be considered in order to perform a complete search.
N	H10F39/80		Group H10F 39/80 is impacted by reclassification into groups H10F 39/802, H10F 39/8023, H10F 39/8027, H10F 39/803, H10F 39/8033, H10F 39/8037, H10F 39/80373, H10F 39/80377, H10F 39/804, H10F 39/805, H10F 39/8053, H10F 39/8057, H10F 39/806, H10F 39/8063, H10F 39/8067, H10F 39/807, H10F 39/809, H10F 39/811, H10F 39/812 and H10F 39/813. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F39/802		Groups H10F 39/802-H10F 39/8027 are incomplete pending reclassification of documents from group H10F 39/80. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F39/803		Groups H10F 39/803-H10F 39/80377 are incomplete pending reclassification of documents from group H10F 39/80. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F39/804		Group H10F 39/804 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/804 should be considered in order to perform a complete search.
N	H10F39/805		Groups H10F 39/805-H10F 39/8057 are incomplete pending reclassification of documents from group H10F 39/80. All groups listed in this Warning should be considered in order to perform a complete search.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
N	H10F39/806		Groups H10F 39/806-H10F 39/8067 are incomplete pending reclassification of documents from group H10F 39/80. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F39/807		Group H10F 39/807 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/807 should be considered in order to perform a complete search.
N	H10F39/809		Group H10F 39/809 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/809 should be considered in order to perform a complete search.
N	H10F39/811		Group H10F 39/811 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/811 should be considered in order to perform a complete search.
N	H10F39/812		Group H10F 39/812 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/812 should be considered in order to perform a complete search.
N	H10F39/813		Group H10F 39/813 is incomplete pending reclassification of documents from group H10F 39/80. Groups H10F 39/80 and H10F 39/813 should be considered in order to perform a complete search.
N	H10F71/00		Group H10F 71/00 is impacted by reclassification into groups H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/135 and H10F 71/136. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F71/10		Group H10F 71/10 is impacted by reclassification into groups H10F 71/103, H10F 71/1035, H10F 71/107, H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/135, H10F 71/136,

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			H10F 71/137, H10F 71/1375, H10F 71/138, H10F 71/1385, H10F 71/139 and H10F 71/1395. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10F71/103		Groups H10F 71/103 and H10F 71/1035 are incomplete pending reclassification of documents from group H10F 71/10. Groups H10F 71/10, H10F 71/103 and H10F 71/1035 should be considered in order to perform a complete search.
N	H10F71/107		Group H10F 71/107 is incomplete pending reclassification of documents from group H10F 71/10. Groups H10F 71/10 and H10F 71/107 should be considered in order to perform a complete search.
N	H10F71/128		Group H10F 71/128 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/128 should be considered in order to perform a complete search.
N	H10F71/129		Group H10F 71/129 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/129 should be considered in order to perform a complete search.
N	H10F71/131		Group H10F 71/131 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/131 should be considered in order to perform a complete search.
N	H10F71/132		Group H10F 71/132 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/132 should be considered in order to perform a complete search.
N	H10F71/133		Group H10F 71/133 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/133 should

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Type*</u>	<u>Location</u>	<u>Old Warning</u>	<u>New/Modified Warning</u>
			be considered in order to perform a complete search.
N	H10F71/134		Group H10F 71/134 is incomplete pending reclassification of documents from group H10F 71/00. Groups H10F 71/00 and H10F 71/134 should be considered in order to perform a complete search.
N	H10F71/135		Group H10F 71/135 is incomplete pending reclassification of documents from groups H10F 71/00 and H10F 71/10. Groups H10F 71/00, H10F 71/10 and H10F 71/135 should be considered in order to perform a complete search.
N	H10F71/136		Group H10F 71/136 is incomplete pending reclassification of documents from group H10F 71/00. Groups H10F 71/00 and H10F 71/136 should be considered in order to perform a complete search.
N	H10F71/137		Groups H10F 71/137 and H10F 71/1375 are incomplete pending reclassification of documents from group H10F 71/10. Groups H10F 71/10, H10F 71/137 and H10F 71/1375 should be considered in order to perform a complete search.
N	H10F71/138		Groups H10F 71/138 and H10F 71/1385 are incomplete pending reclassification of documents from group H10F 71/10. Groups H10F 71/10, H10F 71/138 and H10F 71/1385 should be considered in order to perform a complete search.
N	H10F71/139		Groups H10F 71/139 and H10F 71/1395 are incomplete pending reclassification of documents from group H10F 71/10. Groups H10F 71/10, H10F 71/139 and H10F 71/1395 should be considered in order to perform a complete search.
N	H10F99/00		Group H10F 99/00 is impacted by reclassification into groups H10F 10/00, H10F 19/00, H10F 30/00, H10F 39/00 and H10F 39/10. All groups listed in this Warning should be considered in order to perform a complete search.

*N = new warning, M = modified warning, D = deleted warning

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

NOTE: The "Location" column only requires the symbol PRIOR to the location of the warning. No further directions such as "before" or "after" are required.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

C. New, Modified or Deleted Note(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
N	H01L 21/00		{Due to the ongoing developments in class H10 and related subclasses, the information displayed in notes, references and definitions of this main group and indents may not be entirely accurate. For each specific subject matter referred to in this main group and indents, users are invited to consult the relevant place in class H10 and to consider the class H10 information as correct, in case of conflict}
M	H01L 25/00	1. {This group does not cover: <ul style="list-style-type: none"> • assemblies of electronic memory devices only, which are covered by H10B 80/00; • assemblies of organic devices only, which are covered by groups H10K 19/00, H10K 39/00, H10K 59/00 or H10K 65/00; • assemblies of electric solid-state devices only, which are covered by groups H10N 19/00, H10N 39/00, H10N 59/00, H10N 69/00, H10N 79/00 or H10N 89/00.} 	{Due to the ongoing developments in class H10 and related subclasses, the information displayed in notes, references and definitions of this main group and indents may not be entirely accurate. For each specific subject matter referred to in this main group and indents, users are invited to consult the relevant place in class H10 and to consider the class H10 information as correct, in case of conflict}

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

SUBCLASS H10F - INORGANIC SEMICONDUCTOR DEVICES SENSITIVE TO INFRARED RADIATION, LIGHT, ELECTROMAGNETIC RADIATION OF SHORTER WAVELENGTH OR CORPUSCULAR RADIATION

<u>Type*</u>	<u>Location</u>	<u>Old Note</u>	<u>New/Modified Note</u>
N	H10F		<p>1. This subclass <u>covers</u> inorganic radiation-sensitive semiconductor devices insofar as these devices are specially adapted for:</p> <ul style="list-style-type: none"> - the conversion of the radiation energy into electrical energy; or - the control of electrical energy by such radiation. <p>2. In this subclass, infrared radiation includes wavelengths between about 700 nm and about 1 mm.</p> <p>3. In this subclass, the periodic system used is the I to VIII Group system indicated in the Periodic Table under Note (3) of section C.</p>
N	H10F 77/00		When classifying in this group, the type of device itself, when it is determined to be novel and nonobvious, should be classified in groups H10F 10/00, H10F 19/00, H10F 30/00 or H10F 55/00.
N	H10F 77/12		When classifying in this group, constituents of a material are considered irrespective of any dopants or other impurities.

*N = new note, M = modified note, D = deleted note

NOTE: The "Location" column only requires the symbol PRIOR to the location of the note. No further directions such as "before" or "after" are required.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

D. New, Modified or Deleted Guidance Heading(s)

SUBCLASS H10F - INORGANIC SEMICONDUCTOR DEVICES SENSITIVE TO INFRARED RADIATION, LIGHT, ELECTROMAGNETIC RADIATION OF SHORTER WAVELENGTH OR CORPUSCULAR RADIATION

<u>Type*</u>	<u>Location</u>	<u>Old Guidance Heading</u>	<u>New/Modified Guidance Heading</u>
N	H10F 10/00- H10F 19/00		Photovoltaics
N	H10F 30/00- H10F 39/00		Radiation-controlled devices
N	H10F 55/00- H10F 55/00		Other devices
N	H10F 71/00- H10F 77/00		Manufacture or treatment; Constructional details

*N = new guidance heading, M = modified guidance heading, D = deleted guidance heading

NOTES:

- The "Location" column requires the symbol AFTER the guidance heading location. No further directions such as "before" or "after" are required.

In cases where there may be confusion as to whether a new group falls within the scope of a guidance heading, indicate the guidance heading and whether the group does or does not go with the guidance heading. This can be included in the "Location" column. For example, the guidance heading "Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen" encompasses groups C07C 301/00-395/00 only. If a new group C07C 398/00 is proposed and is included in the guidance heading scope, indicate this in the "Location" column as follows: 398/00 to be included under the guidance heading: "Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen".

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

2. B. DEFINITIONS QUICK FIX

Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L27/14			Delete entire definition
H01L27/142			Delete entire definition
H01L27/144			Delete entire definition
H01L27/1443			Delete entire definition
H01L27/1446			Delete entire definition
H01L27/146			Delete entire definition
H01L27/14601			Delete entire definition
H01L27/14603			Delete entire definition
H01L27/14605			Delete entire definition
H01L27/14607			Delete entire definition
H01L27/14609			Delete entire definition
H01L27/1461			Delete entire definition
H01L27/14612			Delete entire definition
H01L27/14614			Delete entire definition
H01L27/14616			Delete entire definition
H01L27/14618			Delete entire definition
H01L27/1462			Delete entire definition
H01L27/14621			Delete entire definition
H01L27/14623			Delete entire definition
H01L27/14625			Delete entire definition
H01L27/14627			Delete entire definition
H01L27/14629			Delete entire definition
H01L27/1463			Delete entire definition
H01L27/14632			Delete entire definition
H01L27/14634			Delete entire definition
H01L27/14636			Delete entire definition
H01L27/14638			Delete entire definition
H01L27/1464			Delete entire definition
H01L27/14641			Delete entire definition
H01L27/14643			Delete entire definition
H01L27/14645			Delete entire definition
H01L27/14647			Delete entire definition
H01L27/14649			Delete entire definition
H01L27/1465			Delete entire definition
H01L27/14652			Delete entire definition
H01L27/14654			Delete entire definition
H01L27/14656			Delete entire definition
H01L27/14658			Delete entire definition
H01L27/14659			Delete entire definition

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01L27/14661			Delete entire definition
H01L27/14663			Delete entire definition
H01L27/14665			Delete entire definition
H01L27/1467			Delete entire definition
H01L27/14672			Delete entire definition
H01L27/14674			Delete entire definition
H01L27/14676			Delete entire definition
H01L27/14678			Delete entire definition
H01L27/14683			Delete entire definition
H01L27/14685			Delete entire definition
H01L27/14687			Delete entire definition
H01L27/14689			Delete entire definition
H01L27/1469			Delete entire definition
H01L27/148			Delete entire definition
H01L27/14812			Delete entire definition
H01L27/14818			Delete entire definition
H01L27/14825			Delete entire definition
H01L27/14831			Delete entire definition
H01L27/14837			Delete entire definition
H01L27/14843			Delete entire definition
H01L27/1485			Delete entire definition
H01L27/14856			Delete entire definition
H01L27/14862			Delete entire definition
H01L31/00			Delete entire definition
H01L31/02			Delete entire definition
H01L31/02002			Delete entire definition
H01L31/02005			Delete entire definition
H01L31/02008			Delete entire definition
H01L31/02016			Delete entire definition
H01L31/02021			Delete entire definition
H01L31/02024			Delete entire definition
H01L31/02027			Delete entire definition
H01L31/0203			Delete entire definition
H01L31/0216			Delete entire definition
H01L31/02161			Delete entire definition
H01L31/02162			Delete entire definition
H01L31/02164			Delete entire definition
H01L31/02165			Delete entire definition
H01L31/02167			Delete entire definition
H01L31/02168			Delete entire definition
H01L31/0224			Delete entire definition
H01L31/022408			Delete entire definition
H01L31/022425			Delete entire definition
H01L31/022433			Delete entire definition

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01L31/022466			Delete entire definition
H01L31/0232			Delete entire definition
H01L31/02322			Delete entire definition
H01L31/0236			Delete entire definition
H01L31/024			Delete entire definition
H01L31/0248			Delete entire definition
H01L31/0256			Delete entire definition
H01L31/0264			Delete entire definition
H01L31/028			Delete entire definition
H01L31/0284			Delete entire definition
H01L31/02966			Delete entire definition
H01L31/03046			Delete entire definition
H01L31/0321			Delete entire definition
H01L31/0322			Delete entire definition
H01L31/03365			Delete entire definition
H01L31/0352			Delete entire definition
H01L31/035236			Delete entire definition
H01L31/035272			Delete entire definition
H01L31/035281			Delete entire definition
H01L31/03529			Delete entire definition
H01L31/036			Delete entire definition
H01L31/0368			Delete entire definition
H01L31/03682			Delete entire definition
H01L31/0376			Delete entire definition
H01L31/03762			Delete entire definition
H01L31/03767			Delete entire definition
H01L31/0384			Delete entire definition
H01L31/0392			Delete entire definition
H01L31/03921			Delete entire definition
H01L31/04			Delete entire definition
H01L31/041			Delete entire definition
H01L31/042			Delete entire definition
H01L31/044			Delete entire definition
H01L31/0443			Delete entire definition
H01L31/0445			Delete entire definition
H01L31/046			Delete entire definition
H01L31/0463			Delete entire definition
H01L31/0465			Delete entire definition
H01L31/0468			Delete entire definition
H01L31/047			Delete entire definition
H01L31/0475			Delete entire definition
H01L31/048			Delete entire definition
H01L31/049			Delete entire definition
H01L31/05			Delete entire definition

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01L31/052			Delete entire definition
H01L31/0525			Delete entire definition
H01L31/053			Delete entire definition
H01L31/054			Delete entire definition
H01L31/055			Delete entire definition
H01L31/056			Delete entire definition
H01L31/06			Delete entire definition
H01L31/061			Delete entire definition
H01L31/062			Delete entire definition
H01L31/065			Delete entire definition
H01L31/068			Delete entire definition
H01L31/0687			Delete entire definition
H01L31/0693			Delete entire definition
H01L31/07			Delete entire definition
H01L31/072			Delete entire definition
H01L31/0725			Delete entire definition
H01L31/073			Delete entire definition
H01L31/0735			Delete entire definition
H01L31/074			Delete entire definition
H01L31/0745			Delete entire definition
H01L31/0747			Delete entire definition
H01L31/0749			Delete entire definition
H01L31/075			Delete entire definition
H01L31/076			Delete entire definition
H01L31/077			Delete entire definition
H01L31/078			Delete entire definition
H01L31/08			Delete entire definition
H01L31/085			Delete entire definition
H01L31/09			Delete entire definition
H01L31/10			Delete entire definition
H01L31/101			Delete entire definition
H01L31/103			Delete entire definition
H01L31/12			Delete entire definition
H01L31/125			Delete entire definition
H01L31/14			Delete entire definition
H01L31/147			Delete entire definition
H01L31/153			Delete entire definition
H01L31/16			Delete entire definition
H01L31/18			Delete entire definition
H01L31/1804			Delete entire definition
H01L31/1828			Delete entire definition
H01L31/184			Delete entire definition
H01L31/186			Delete entire definition
H01L31/1864			Delete entire definition

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01L31/1868			Delete entire definition
H01L31/1872			Delete entire definition
H01L31/1876			Delete entire definition
H01L31/188			Delete entire definition
H01L31/1884			Delete entire definition
H01L31/20			Delete entire definition
H01L31/202			Delete entire definition
H01L31/206			Delete entire definition
H01L31/208			Delete entire definition

Notes:

Use this Definitions Quick Fix (DQF) table to:

- Delete an entire definition
- Delete an entire section
- Change a reference symbol
- Delete a reference symbol
- Delete text in a References section
- Correct one error in spelling, article use, or verb tense

Otherwise, use the standard template.

Reminder: Never delete Fsymbol definitions.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

3. REVISION CONCORDANCE LIST (RCL)

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 27/14	<administrative transfer to H 10F 99/00>
D	H01L 27/142	<administrative transfer to H 10F 19/50>
D	H01L 27/1421	<administrative transfer to H 10F 19/75>
D	H01L 27/144	<administrative transfer to H 10F 39/10>
D	H01L 27/1443	<administrative transfer to H 10F 39/103>
D	H01L 27/1446	<administrative transfer to H 10F 39/107>
D	H01L 27/146	<administrative transfer to H 10F 39/12>
D	H01L 27/14601	<administrative transfer to H 10F 39/80>
D	H01L 27/14603	<administrative transfer to H 10F 39/802>
D	H01L 27/14605	<administrative transfer to H 10F 39/8023>
D	H01L 27/14607	<administrative transfer to H 10F 39/8027>
D	H01L 27/14609	<administrative transfer to H 10F 39/803>
D	H01L 27/1461	<administrative transfer to H 10F 39/8033>
D	H01L 27/14612	<administrative transfer to H 10F 39/8037>
D	H01L 27/14614	<administrative transfer to H 10F 39/80373>
D	H01L 27/14616	<administrative transfer to H 10F 39/80377>
D	H01L 27/14618	<administrative transfer to H 10F 39/804>
D	H01L 27/1462	<administrative transfer to H 10F 39/805>
D	H01L 27/14621	<administrative transfer to H 10F 39/8053>
D	H01L 27/14623	<administrative transfer to H 10F 39/8057>
D	H01L 27/14625	<administrative transfer to H 10F 39/806>
D	H01L 27/14627	<administrative transfer to H 10F 39/8063>
D	H01L 27/14629	<administrative transfer to H 10F 39/8067>
D	H01L 27/1463	<administrative transfer to H 10F 39/807>
D	H01L 27/14632	<administrative transfer to H 10F 39/026>
D	H01L 27/14634	<administrative transfer to H 10F 39/809>
D	H01L 27/14636	<administrative transfer to H 10F 39/811>
D	H01L 27/14638	<administrative transfer to H 10F 39/812>
D	H01L 27/1464	<administrative transfer to H 10F 39/199>
D	H01L 27/14641	<administrative transfer to H 10F 39/813>
D	H01L 27/14643	<administrative transfer to H 10F 39/18>
D	H01L 27/14645	<administrative transfer to H 10F 39/182>
D	H01L 27/14647	<administrative transfer to H 10F 39/1825>
D	H01L 27/14649	<administrative transfer to H 10F 39/184>
D	H01L 27/1465	<administrative transfer to H 10F 39/1843>
D	H01L 27/14652	<administrative transfer to H 10F 39/1847>
D	H01L 27/14654	<administrative transfer to H 10F 39/186>
D	H01L 27/14656	<administrative transfer to H 10F 39/1865>
D	H01L 27/14658	<administrative transfer to H 10F 39/189>
D	H01L 27/14659	<administrative transfer to H 10F 39/1892>
D	H01L 27/14661	<administrative transfer to H 10F 39/1895>
D	H01L 27/14663	<administrative transfer to H 10F 39/1898>
D	H01L 27/14665	<administrative transfer to H 10F 39/191>
D	H01L 27/14667	<administrative transfer to H 10F 39/192>
D	H01L 27/14669	<administrative transfer to H 10F 39/193>
D	H01L 27/1467	<administrative transfer to H 10F 39/1935>
D	H01L 27/14672	<administrative transfer to H 10F 39/194>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 27/14674	<administrative transfer to H10F 39/1945>
D	H01L 27/14676	<administrative transfer to H10F 39/195>
D	H01L 27/14678	<administrative transfer to H10F 39/198>
D	H01L 27/14679	<administrative transfer to H10F 39/196>
D	H01L 27/14681	<administrative transfer to H10F 39/197>
D	H01L 27/14683	<administrative transfer to H10F 39/011>
D	H01L 27/14685	<administrative transfer to H10F 39/024>
D	H01L 27/14687	<administrative transfer to H10F 39/026>
D	H01L 27/14689	<administrative transfer to H10F 39/014>
D	H01L 27/1469	<administrative transfer to H10F 39/018>
D	H01L 27/14692	<administrative transfer to H10F 39/016>
D	H01L 27/14694	<administrative transfer to H10F 39/021>
D	H01L 27/14696	<administrative transfer to H10F 39/022>
D	H01L 27/14698	<administrative transfer to H10F 39/028>
D	H01L 27/148	<administrative transfer to H10F 39/15>
D	H01L 27/14806	<administrative transfer to H10F 39/80>
D	H01L 27/14812	<administrative transfer to H10F 39/151>
D	H01L 27/14818	<administrative transfer to H10F 39/1515>
D	H01L 27/14825	<administrative transfer to H10F 39/152>
D	H01L 27/14831	<administrative transfer to H10F 39/153>
D	H01L 27/14837	<administrative transfer to H10F 39/1532>
D	H01L 27/14843	<administrative transfer to H10F 39/1534>
D	H01L 27/1485	<administrative transfer to H10F 39/1536>
D	H01L 27/14856	<administrative transfer to H10F 39/1538>
D	H01L 27/14862	<administrative transfer to H10F 39/154>
D	H01L 27/14868	<administrative transfer to H10F 39/156>
D	H01L 27/14875	<administrative transfer to H10F 39/157>
D	H01L 27/14881	<administrative transfer to H10F 39/1575>
D	H01L 27/14887	<administrative transfer to H10F 39/158>
D	H01L 27/14893	<administrative transfer to H10F 39/159>
D	H01L 31/00	<administrative transfer to H10F 99/00>
D	H01L 31/02	<administrative transfer to H10F 77/00>
D	H01L 31/02002	<administrative transfer to H10F 77/93>
D	H01L 31/02005	<administrative transfer to H10F 77/933>
D	H01L 31/02008	<administrative transfer to H10F 77/935>
D	H01L 31/0201	<administrative transfer to H10F 77/937>
D	H01L 31/02013	<administrative transfer to H10F 77/939>
D	H01L 31/02016	<administrative transfer to H10F 77/95>
D	H01L 31/02019	<administrative transfer to H10F 77/953>
D	H01L 31/02021	<administrative transfer to H10F 77/955>
D	H01L 31/02024	<administrative transfer to H10F 77/957>
D	H01L 31/02027	<administrative transfer to H10F 77/959>
D	H01L 31/0203	<administrative transfer to H10F 77/50>
D	H01L 31/0216	<administrative transfer to H10F 77/30>
D	H01L 31/02161	<administrative transfer to H10F 77/306>
D	H01L 31/02162	<administrative transfer to H10F 77/331>
D	H01L 31/02164	<administrative transfer to H10F 77/334>
D	H01L 31/02165	<administrative transfer to H10F 77/337>
D	H01L 31/02167	<administrative transfer to H10F 77/311>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 31/02168	<administrative transfer to H10F 77/315>
D	H01L 31/0224	<administrative transfer to H10F 77/20>
D	H01L 31/022408	<administrative transfer to H10F 77/206>
D	H01L 31/022416	<administrative transfer to H10F 77/241>
D	H01L 31/022425	<administrative transfer to H10F 77/211>
D	H01L 31/022433	<administrative transfer to H10F 77/215>
D	H01L 31/022441	<administrative transfer to H10F 77/219>
D	H01L 31/02245	<administrative transfer to H10F 77/223>
D	H01L 31/022458	<administrative transfer to H10F 77/227>
D	H01L 31/022466	<administrative transfer to H10F 77/244>
D	H01L 31/022475	<administrative transfer to H10F 77/247>
D	H01L 31/022483	<administrative transfer to H10F 77/251>
D	H01L 31/022491	<administrative transfer to H10F 77/254>
D	H01L 31/0232	<administrative transfer to H10F 77/40>
D	H01L 31/02322	<administrative transfer to H10F 77/496>
D	H01L 31/02325	<administrative transfer to H10F 77/407>
D	H01L 31/02327	<administrative transfer to H10F 77/413>
D	H01L 31/0236	<administrative transfer to H10F 77/70>
D	H01L 31/02363	<administrative transfer to H10F 77/703>
D	H01L 31/02366	<administrative transfer to H10F 77/707>
D	H01L 31/024	<administrative transfer to H10F 77/60>
D	H01L 31/0248	<administrative transfer to H10F 77/10>
D	H01L 31/0256	<administrative transfer to H10F 77/12>
D	H01L 31/0264	<administrative transfer to H10F 77/12>
D	H01L 31/0272	<administrative transfer to H10F 77/121>
D	H01L 31/02725	<administrative transfer to H10F 77/1215>
D	H01L 31/028	<administrative transfer to H10F 77/122>
D	H01L 31/0284	<administrative transfer to H10F 77/1228>
D	H01L 31/0288	<administrative transfer to H10F 77/1223>
D	H01L 31/0296	<administrative transfer to H10F 77/123>
D	H01L 31/02963	<administrative transfer to H10F 77/1233>
D	H01L 31/02966	<administrative transfer to H10F 77/1237>
D	H01L 31/0304	<administrative transfer to H10F 77/124>
D	H01L 31/03042	<administrative transfer to H10F 77/1243>
D	H01L 31/03044	<administrative transfer to H10F 77/1246>
D	H01L 31/03046	<administrative transfer to H10F 77/1248>
D	H01L 31/03048	<administrative transfer to H10F 77/12485>
D	H01L 31/0312	<administrative transfer to H10F 77/1226>
D	H01L 31/03125	<administrative transfer to H10F 77/1227>
D	H01L 31/032	<administrative transfer to H10F 77/12>
D	H01L 31/0321	<administrative transfer to H10F 77/12>
D	H01L 31/0322	<administrative transfer to H10F 77/126>
D	H01L 31/0323	<administrative transfer to H10F 77/1265>
D	H01L 31/0324	<administrative transfer to H10F 77/127>
D	H01L 31/0325	<administrative transfer to H10F 77/1275>
D	H01L 31/0326	<administrative transfer to H10F 77/128>
D	H01L 31/0327	<administrative transfer to H10F 77/1285>
D	H01L 31/0328	<administrative transfer to H10F 77/12>
D	H01L 31/0336	<administrative transfer to H10F 10/16>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 31/03365	<administrative transfer to H10F 10/169>
D	H01L 2031/0344	<no transfer>
D	H01L 31/0352	<administrative transfer to H10F 77/14>
D	H01L 31/035209	<administrative transfer to H10F 77/143>
D	H01L 31/035218	<administrative transfer to H10F 77/1433>
D	H01L 31/035227	<administrative transfer to H10F 77/1437>
D	H01L 31/035236	<administrative transfer to H10F 77/146>
D	H01L 31/035245	<administrative transfer to H10F 77/1462>
D	H01L 31/035254	<administrative transfer to H10F 77/1465>
D	H01L 31/035263	<administrative transfer to H10F 77/1468>
D	H01L 31/035272	<administrative transfer to H10F 77/14>
D	H01L 31/035281	<administrative transfer to H10F 77/147>
D	H01L 31/03529	<administrative transfer to H10F 77/148>
D	H01L 31/036	<administrative transfer to H10F 77/16>
D	H01L 31/0368	<administrative transfer to H10F 77/164>
D	H01L 31/03682	<administrative transfer to H10F 77/1642>
D	H01L 31/03685	<administrative transfer to H10F 77/1645>
D	H01L 31/03687	<administrative transfer to H10F 77/1648>
D	H01L 31/0376	<administrative transfer to H10F 77/166>
D	H01L 31/03762	<administrative transfer to H10F 77/1662>
D	H01L 31/03765	<administrative transfer to H10F 77/1665>
D	H01L 31/03767	<administrative transfer to H10F 77/1668>
D	H01L 31/0384	<administrative transfer to H10F 77/162>
D	H01L 31/03845	<administrative transfer to H10F 77/1625>
D	H01L 31/0392	<administrative transfer to H10F 77/169>
D	H01L 31/03921	<administrative transfer to H10F 77/1692>
D	H01L 31/03923	<administrative transfer to H10F 77/1694>
D	H01L 31/03925	<administrative transfer to H10F 77/1696>
D	H01L 31/03926	<administrative transfer to H10F 77/1698>
D	H01L 31/03928	<administrative transfer to H10F 77/1699>
D	H01L 31/04	<administrative transfer to H10F 10/00>
D	H01L 31/041	<administrative transfer to H10F 77/80>
D	H01L 31/042	<administrative transfer to H10F 19/00>
D	H01L 31/043	<administrative transfer to H10F 19/40>
D	H01L 31/044	<administrative transfer to H10F 19/70>
D	H01L 31/0443	<administrative transfer to H10F 19/75>
D	H01L 31/0445	<administrative transfer to H10F 19/30>
D	H01L 31/046	<administrative transfer to H10F 19/31>
D	H01L 31/0463	<administrative transfer to H10F 19/33>
D	H01L 31/0465	<administrative transfer to H10F 19/35>
D	H01L 31/0468	<administrative transfer to H10F 19/37>
D	H01L 31/047	<administrative transfer to H10F 19/10>
D	H01L 31/0475	<administrative transfer to H10F 19/20>
D	H01L 31/048	<administrative transfer to H10F 19/80>
D	H01L 31/0481	<administrative transfer to H10F 19/804>
D	H01L 31/0488	<administrative transfer to H10F 19/807>
D	H01L 31/049	<administrative transfer to H10F 19/85>
D	H01L 31/05	<administrative transfer to H10F 19/90>
D	H01L 31/0504	<administrative transfer to H10F 19/902>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 31/0508	<administrative transfer to H10F 19/904>
D	H01L 31/0512	<administrative transfer to H10F 19/906>
D	H01L 31/0516	<administrative transfer to H10F 19/908>
D	H01L 31/052	<administrative transfer to H10F 77/63>
D	H01L 31/0521	<administrative transfer to H10F 77/68>
D	H01L 31/0525	<administrative transfer to H10F 77/67>
D	H01L 31/053	<administrative transfer to H10F 77/90>
D	H01L 31/054	<administrative transfer to H10F 77/42>
D	H01L 31/0543	<administrative transfer to H10F 77/484>
D	H01L 31/0547	<administrative transfer to H10F 77/488>
D	H01L 31/0549	<administrative transfer to H10F 77/492>
D	H01L 31/055	<administrative transfer to H10F 77/45>
D	H01L 31/056	<administrative transfer to H10F 77/48>
D	H01L 31/06	<administrative transfer to H10F 10/10>
D	H01L 31/061	<administrative transfer to H10F 10/11>
D	H01L 31/062	<administrative transfer to H10F 10/12>
D	H01L 31/065	<administrative transfer to H10F 10/13>
D	H01L 31/068	<administrative transfer to H10F 10/14>
D	H01L 31/0682	<administrative transfer to H10F 10/146>
D	H01L 31/0684	<administrative transfer to H10F 10/148>
D	H01L 31/0687	<administrative transfer to H10F 10/142>
D	H01L 31/06875	<administrative transfer to H10F 10/1425>
D	H01L 31/0693	<administrative transfer to H10F 10/144>
D	H01L 31/07	<administrative transfer to H10F 10/18>
D	H01L 31/072	<administrative transfer to H10F 10/16>
D	H01L 31/0725	<administrative transfer to H10F 10/161>
D	H01L 31/073	<administrative transfer to H10F 10/162>
D	H01L 31/0735	<administrative transfer to H10F 10/163>
D	H01L 31/074	<administrative transfer to H10F 10/164>
D	H01L 31/0745	<administrative transfer to H10F 10/165>
D	H01L 31/0747	<administrative transfer to H10F 10/166>
D	H01L 31/0749	<administrative transfer to H10F 10/167>
D	H01L 31/075	<administrative transfer to H10F 10/17>
D	H01L 31/076	<administrative transfer to H10F 10/172>
D	H01L 31/077	<administrative transfer to H10F 10/174>
D	H01L 31/078	<administrative transfer to H10F 10/19>
D	H01L 31/08	<administrative transfer to H10F 30/00>
D	H01L 31/085	<administrative transfer to H10F 30/301>
D	H01L 31/09	<administrative transfer to H10F 30/10>
D	H01L 31/095	<administrative transfer to H10F 30/15>
D	H01L 31/10	<administrative transfer to H10F 30/20>
D	H01L 31/101	<administrative transfer to H10F 30/21>
D	H01L 31/1013	<administrative transfer to H10F 30/288>
D	H01L 31/1016	<administrative transfer to H10F 30/289>
D	H01L 31/102	<administrative transfer to H10F 30/22>
D	H01L 31/1025	<administrative transfer to H10F 30/2205>
D	H01L 31/103	<administrative transfer to H10F 30/221>
D	H01L 31/1032	<administrative transfer to H10F 30/2212>
D	H01L 31/1035	<administrative transfer to H10F 30/2215>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 31/1037	<administrative transfer to H10F 30/2218>
D	H01L 31/105	<administrative transfer to H10F 30/223>
D	H01L 31/1055	<administrative transfer to H10F 30/2235>
D	H01L 31/107	<administrative transfer to H10F 30/225>
D	H01L 31/1075	<administrative transfer to H10F 30/2255>
D	H01L 31/108	<administrative transfer to H10F 30/227>
D	H01L 31/1085	<administrative transfer to H10F 30/2275>
D	H01L 31/109	<administrative transfer to H10F 30/222>
D	H01L 31/11	<administrative transfer to H10F 30/24>
D	H01L 31/1105	<administrative transfer to H10F 30/245>
D	H01L 31/111	<administrative transfer to H10F 30/26>
D	H01L 31/1113	<administrative transfer to H10F 30/263>
D	H01L 31/1116	<administrative transfer to H10F 30/2635>
D	H01L 31/112	<administrative transfer to H10F 30/28>
D	H01L 31/1121	<administrative transfer to H10F 30/283>
D	H01L 31/1122	<administrative transfer to H10F 30/2837>
D	H01L 31/1123	<administrative transfer to H10F 30/2843>
D	H01L 31/1124	<administrative transfer to H10F 30/285>
D	H01L 31/1125	<administrative transfer to H10F 30/2857>
D	H01L 31/1126	<administrative transfer to H10F 30/2863>
D	H01L 31/1127	<administrative transfer to H10F 30/287>
D	H01L 31/1128	<administrative transfer to H10F 30/2873>
D	H01L 31/1129	<administrative transfer to H10F 30/2877>
D	H01L 31/113	<administrative transfer to H10F 30/2823>
D	H01L 31/1133	<administrative transfer to H10F 30/2823>
D	H01L 31/1136	<administrative transfer to H10F 30/282>
D	H01L 31/115	<administrative transfer to H10F 30/29>
D	H01L 31/117	<administrative transfer to H10F 30/292>
D	H01L 31/1175	<administrative transfer to H10F 30/2925>
D	H01L 31/118	<administrative transfer to H10F 30/295>
D	H01L 31/1185	<administrative transfer to H10F 30/2955>
D	H01L 31/119	<administrative transfer to H10F 30/298>
D	H01L 31/12	<administrative transfer to H10F 55/00>
D	H01L 31/125	<administrative transfer to H10F 55/18>
D	H01L 31/14	<administrative transfer to H10F 55/10>
D	H01L 31/141	<administrative transfer to H10F 55/16>
D	H01L 31/143	<administrative transfer to H10F 55/165>
D	H01L 31/145	<administrative transfer to H10F 55/17>
D	H01L 31/147	<administrative transfer to H10F 55/15>
D	H01L 31/153	<administrative transfer to H10F 55/155>
D	H01L 31/16	<administrative transfer to H10F 55/20>
D	H01L 31/161	<administrative transfer to H10F 55/205>
D	H01L 31/162	<administrative transfer to H10F 55/207>
D	H01L 31/164	<administrative transfer to H10F 55/208>
D	H01L 31/165	<administrative transfer to H10F 55/26>
D	H01L 31/167	<administrative transfer to H10F 55/25>
D	H01L 31/173	<administrative transfer to H10F 55/255>
D	H01L 31/18	<administrative transfer to H10F 71/00>
D	H01L 31/1804	<administrative transfer to H10F 71/121>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 31/1808	<administrative transfer to H10F 71/1212>
D	H01L 31/1812	<administrative transfer to H10F 71/1215>
D	H01L 31/1816	<administrative transfer to H10F 71/1218>
D	H01L 31/182	<administrative transfer to H10F 71/1221>
D	H01L 31/1824	<administrative transfer to H10F 71/1224>
D	H01L 31/1828	<administrative transfer to H10F 71/125>
D	H01L 31/1832	<administrative transfer to H10F 71/1253>
D	H01L 31/1836	<administrative transfer to H10F 71/1257>
D	H01L 31/184	<administrative transfer to H10F 71/127>
D	H01L 31/1844	<administrative transfer to H10F 71/1272>
D	H01L 31/1848	<administrative transfer to H10F 71/1274>
D	H01L 31/1852	<administrative transfer to H10F 71/1276>
D	H01L 31/1856	<administrative transfer to H10F 71/1278>
D	H01L 31/186	<administrative transfer to H10F 71/00>
D	H01L 31/1864	<administrative transfer to H10F 71/128>
D	H01L 31/1868	<administrative transfer to H10F 71/129>
D	H01L 31/1872	<administrative transfer to H10F 71/131>
D	H01L 31/1876	<administrative transfer to H10F 71/137>
D	H01L 31/188	<administrative transfer to H10F 71/1375>
D	H01L 31/1884	<administrative transfer to H10F 71/138>
D	H01L 31/1888	<administrative transfer to H10F 71/1385>
D	H01L 31/1892	<administrative transfer to H10F 71/139>
D	H01L 31/1896	<administrative transfer to H10F 71/1395>
D	H01L 31/20	<administrative transfer to H10F 71/10>
D	H01L 31/202	<administrative transfer to H10F 71/103>
D	H01L 31/204	<administrative transfer to H10F 71/1035>
D	H01L 31/206	<administrative transfer to H10F 71/107>
D	H01L 31/208	<administrative transfer to H10F 71/10>
Q	H10F 39/80	H10F 39/80, H10F 39/802, H10F 39/8023, H10F 39/8027, H10F 39/803, H10F 39/8033, H10F 39/8037, H10F 39/80373, H10F 39/80377, H10F 39/804, H10F 39/805, H10F 39/8053, H10F 39/8057, H10F 39/806, H10F 39/8063, H10F 39/8067, H10F 39/807, H10F 39/809, H10F 39/811, H10F 39/812, H10F 39/813
Q	H10F 71/00	H10F 71/00, H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/135, H10F 71/136
Q	H10F 71/10	H10F 71/10, H10F 71/103, H10F 71/1035, H10F 71/107, H10F 71/128, H10F 71/129, H10F 71/131, H10F 71/132, H10F 71/133, H10F 71/134, H10F 71/136, H10F 71/135, H10F 71/137, H10F 71/1375, H10F 71/138, H10F 71/1385, H10F 71/139, H10F 71/1395
Q	H10F 99/00	H10F 99/00, H10F 10/00, H10F 19/00, H10F 30/00, H10F 39/00, H10F 39/10

* C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed.

NOTES:

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

- Only C, D, F, and Q type entries are included in the table above.
- When multiple symbols are included in the “To” column, do not use ranges of symbols.
- For administrative transfer of documents, the following text should be used: “<administrative transfer to XX>”, “<administrative transfer to XX and YY simultaneously>”, or “<administrative transfer to XX, YY, ...and ZZ simultaneously>” when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be “additional information”.
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations “ADD” or “INV”: <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or < administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the “D” entries of 2000-series or Y-series groups may not require a destination (“To”) symbol, however it is required to specify “<no transfer>” in the “To” column for such cases.
- RCL is not needed for finalisation projects.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 27/14		DELETE
H01L 27/142		DELETE
H01L 27/1421		DELETE
H01L 27/144		DELETE
H01L 27/1443		DELETE
H01L 27/1446		DELETE
H01L 27/146		DELETE
H01L 27/14601		DELETE
H01L 27/14603		DELETE
H01L 27/14605		DELETE
H01L 27/14607		DELETE
H01L 27/14609		DELETE
H01L 27/1461		DELETE
H01L 27/14612		DELETE
H01L 27/14614		DELETE
H01L 27/14616		DELETE
H01L 27/14618		DELETE
H01L 27/1462		DELETE
H01L 27/14621		DELETE
H01L 27/14623		DELETE
H01L 27/14625		DELETE
H01L 27/14627		DELETE
H01L 27/14629		DELETE
H01L 27/1463		DELETE
H01L 27/14632		DELETE
H01L 27/14634		DELETE
H01L 27/14636		DELETE
H01L 27/14638		DELETE
H01L 27/1464		DELETE
H01L 27/14641		DELETE
H01L 27/14643		DELETE
H01L 27/14645		DELETE
H01L 27/14647		DELETE
H01L 27/14649		DELETE
H01L 27/1465		DELETE
H01L 27/14652		DELETE
H01L 27/14654		DELETE
H01L 27/14656		DELETE
H01L 27/14658		DELETE
H01L 27/14659		DELETE
H01L 27/14661		DELETE
H01L 27/14663		DELETE
H01L 27/14665		DELETE
H01L 27/14667		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 27/14669		DELETE
H01L 27/1467		DELETE
H01L 27/14672		DELETE
H01L 27/14674		DELETE
H01L 27/14676		DELETE
H01L 27/14678		DELETE
H01L 27/14679		DELETE
H01L 27/14681		DELETE
H01L 27/14683		DELETE
H01L 27/14685		DELETE
H01L 27/14687		DELETE
H01L 27/14689		DELETE
H01L 27/1469		DELETE
H01L 27/14692		DELETE
H01L 27/14694		DELETE
H01L 27/14696		DELETE
H01L 27/14698		DELETE
H01L 27/148		DELETE
H01L 27/14806		DELETE
H01L 27/14812		DELETE
H01L 27/14818		DELETE
H01L 27/14825		DELETE
H01L 27/14831		DELETE
H01L 27/14837		DELETE
H01L 27/14843		DELETE
H01L 27/1485		DELETE
H01L 27/14856		DELETE
H01L 27/14862		DELETE
H01L 27/14868		DELETE
H01L 27/14875		DELETE
H01L 27/14881		DELETE
H01L 27/14887		DELETE
H01L 27/14893		DELETE
H01L 31/00		DELETE
H01L 31/02		DELETE
H01L 31/02002		DELETE
H01L 31/02005		DELETE
H01L 31/02008		DELETE
H01L 31/0201		DELETE
H01L 31/02013		DELETE
H01L 31/02016		DELETE
H01L 31/02019		DELETE
H01L 31/02021		DELETE
H01L 31/02024		DELETE
H01L 31/02027		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/0203		DELETE
H01L 31/0216		DELETE
H01L 31/02161		DELETE
H01L 31/02162		DELETE
H01L 31/02164		DELETE
H01L 31/02165		DELETE
H01L 31/02167		DELETE
H01L 31/02168		DELETE
H01L 31/0224		DELETE
H01L 31/022408		DELETE
H01L 31/022416		DELETE
H01L 31/022425		DELETE
H01L 31/022433		DELETE
H01L 31/022441		DELETE
H01L 31/02245		DELETE
H01L 31/022458		DELETE
H01L 31/022466		DELETE
H01L 31/022475		DELETE
H01L 31/022483		DELETE
H01L 31/022491		DELETE
H01L 31/0232		DELETE
H01L 31/02322		DELETE
H01L 31/02325		DELETE
H01L 31/02327		DELETE
H01L 31/0236		DELETE
H01L 31/02363		DELETE
H01L 31/02366		DELETE
H01L 31/024		DELETE
H01L 31/0248		DELETE
H01L 31/0256		DELETE
H01L 31/0264		DELETE
H01L 31/0272		DELETE
H01L 31/02725		DELETE
H01L 31/028		DELETE
H01L 31/0284		DELETE
H01L 31/0288		DELETE
H01L 31/0296		DELETE
H01L 31/02963		DELETE
H01L 31/02966		DELETE
H01L 31/0304		DELETE
H01L 31/03042		DELETE
H01L 31/03044		DELETE
H01L 31/03046		DELETE
H01L 31/03048		DELETE
H01L 31/0312		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/03125		DELETE
H01L 31/032		DELETE
H01L 31/0321		DELETE
H01L 31/0322		DELETE
H01L 31/0323		DELETE
H01L 31/0324		DELETE
H01L 31/0325		DELETE
H01L 31/0326		DELETE
H01L 31/0327		DELETE
H01L 31/0328		DELETE
H01L 31/0336		DELETE
H01L 31/03365		DELETE
H01L 2031/0344		DELETE
H01L 31/0352		DELETE
H01L 31/035209		DELETE
H01L 31/035218		DELETE
H01L 31/035227		DELETE
H01L 31/035236		DELETE
H01L 31/035245		DELETE
H01L 31/035254		DELETE
H01L 31/035263		DELETE
H01L 31/035272		DELETE
H01L 31/035281		DELETE
H01L 31/03529		DELETE
H01L 31/036		DELETE
H01L 31/0368		DELETE
H01L 31/03682		DELETE
H01L 31/03685		DELETE
H01L 31/03687		DELETE
H01L 31/0376		DELETE
H01L 31/03762		DELETE
H01L 31/03765		DELETE
H01L 31/03767		DELETE
H01L 31/0384		DELETE
H01L 31/03845		DELETE
H01L 31/0392		DELETE
H01L 31/03921		DELETE
H01L 31/03923		DELETE
H01L 31/03925		DELETE
H01L 31/03926		DELETE
H01L 31/03928		DELETE
H01L 31/04		DELETE
H01L 31/041		DELETE
H01L 31/042		DELETE
H01L 31/043		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/044		DELETE
H01L 31/0443		DELETE
H01L 31/0445		DELETE
H01L 31/046		DELETE
H01L 31/0463		DELETE
H01L 31/0465		DELETE
H01L 31/0468		DELETE
H01L 31/047		DELETE
H01L 31/0475		DELETE
H01L 31/048		DELETE
H01L 31/0481		DELETE
H01L 31/0488		DELETE
H01L 31/049		DELETE
H01L 31/05		DELETE
H01L 31/0504		DELETE
H01L 31/0508		DELETE
H01L 31/0512		DELETE
H01L 31/0516		DELETE
H01L 31/052		DELETE
H01L 31/0521		DELETE
H01L 31/0525		DELETE
H01L 31/053		DELETE
H01L 31/054		DELETE
H01L 31/0543		DELETE
H01L 31/0547		DELETE
H01L 31/0549		DELETE
H01L 31/055		DELETE
H01L 31/056		DELETE
H01L 31/06		DELETE
H01L 31/061		DELETE
H01L 31/062		DELETE
H01L 31/065		DELETE
H01L 31/068		DELETE
H01L 31/0682		DELETE
H01L 31/0684		DELETE
H01L 31/0687		DELETE
H01L 31/06875		DELETE
H01L 31/0693		DELETE
H01L 31/07		DELETE
H01L 31/072		DELETE
H01L 31/0725		DELETE
H01L 31/073		DELETE
H01L 31/0735		DELETE
H01L 31/074		DELETE
H01L 31/0745		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/0747		DELETE
H01L 31/0749		DELETE
H01L 31/075		DELETE
H01L 31/076		DELETE
H01L 31/077		DELETE
H01L 31/078		DELETE
H01L 31/08		DELETE
H01L 31/085		DELETE
H01L 31/09		DELETE
H01L 31/095		DELETE
H01L 31/10		DELETE
H01L 31/101		DELETE
H01L 31/1013		DELETE
H01L 31/1016		DELETE
H01L 31/102		DELETE
H01L 31/1025		DELETE
H01L 31/103		DELETE
H01L 31/1032		DELETE
H01L 31/1035		DELETE
H01L 31/1037		DELETE
H01L 31/105		DELETE
H01L 31/1055		DELETE
H01L 31/107		DELETE
H01L 31/1075		DELETE
H01L 31/108		DELETE
H01L 31/1085		DELETE
H01L 31/109		DELETE
H01L 31/11		DELETE
H01L 31/1105		DELETE
H01L 31/111		DELETE
H01L 31/1113		DELETE
H01L 31/1116		DELETE
H01L 31/112		DELETE
H01L 31/1121		DELETE
H01L 31/1122		DELETE
H01L 31/1123		DELETE
H01L 31/1124		DELETE
H01L 31/1125		DELETE
H01L 31/1126		DELETE
H01L 31/1127		DELETE
H01L 31/1128		DELETE
H01L 31/1129		DELETE
H01L 31/113		DELETE
H01L 31/1133		DELETE
H01L 31/1136		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/115		DELETE
H01L 31/117		DELETE
H01L 31/1175		DELETE
H01L 31/118		DELETE
H01L 31/1185		DELETE
H01L 31/119		DELETE
H01L 31/12		DELETE
H01L 31/125		DELETE
H01L 31/14		DELETE
H01L 31/141		DELETE
H01L 31/143		DELETE
H01L 31/145		DELETE
H01L 31/147		DELETE
H01L 31/153		DELETE
H01L 31/16		DELETE
H01L 31/161		DELETE
H01L 31/162		DELETE
H01L 31/164		DELETE
H01L 31/165		DELETE
H01L 31/167		DELETE
H01L 31/173		DELETE
H01L 31/18		DELETE
H01L 31/1804		DELETE
H01L 31/1808		DELETE
H01L 31/1812		DELETE
H01L 31/1816		DELETE
H01L 31/182		DELETE
H01L 31/1824		DELETE
H01L 31/1828		DELETE
H01L 31/1832		DELETE
H01L 31/1836		DELETE
H01L 31/184		DELETE
H01L 31/1844		DELETE
H01L 31/1848		DELETE
H01L 31/1852		DELETE
H01L 31/1856		DELETE
H01L 31/186		DELETE
H01L 31/1864		DELETE
H01L 31/1868		DELETE
H01L 31/1872		DELETE
H01L 31/1876		DELETE
H01L 31/188		DELETE
H01L 31/1884		DELETE
H01L 31/1888		DELETE
H01L 31/1892		DELETE

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H01L 31/1896		DELETE
H01L 31/20		DELETE
H01L 31/202		DELETE
H01L 31/204		DELETE
H01L 31/206		DELETE
H01L 31/208		DELETE
H10F 10/00	H10F 10/00	NEW
H10F 10/10	H10F 10/10	NEW
H10F 10/11	H10F 10/11	NEW
H10F 10/12	H10F 10/12	NEW
H10F 10/13	H10F 10/13	NEW
H10F 10/14	H10F 10/14	NEW
H10F 10/142	H10F 10/142	NEW
H10F 10/1425	H10F10/142	NEW
H10F 10/144	H10F 10/144	NEW
H10F 10/146	H10F10/14	NEW
H10F 10/148	H10F10/14	NEW
H10F 10/16	H10F 10/16	NEW
H10F 10/161	H10F 10/161	NEW
H10F 10/162	H10F 10/162	NEW
H10F 10/163	H10F 10/163	NEW
H10F 10/164	H10F 10/164	NEW
H10F 10/165	H10F 10/165	NEW
H10F 10/166	H10F 10/166	NEW
H10F 10/167	H10F 10/167	NEW
H10F 10/169	H10F10/16	NEW
H10F 10/17	H10F 10/17	NEW
H10F 10/172	H10F 10/172	NEW
H10F 10/174	H10F 10/174	NEW
H10F 10/18	H10F 10/18	NEW
H10F 10/19	H10F 10/19	NEW
H10F 19/00	H10F 19/00	NEW
H10F 19/10	H10F 19/10	NEW
H10F 19/20	H10F 19/20	NEW
H10F 19/30	H10F 19/30	NEW
H10F 19/31	H10F 19/31	NEW
H10F 19/33	H10F 19/33	NEW
H10F 19/35	H10F 19/35	NEW
H10F 19/37	H10F 19/37	NEW
H10F 19/40	H10F 19/40	NEW
H10F 19/50	H10F 19/50	NEW
H10F 19/70	H10F 19/70	NEW
H10F 19/75	H10F 19/75	NEW
H10F 19/80	H10F 19/80	NEW
H10F 19/804	H10F19/80	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 19/807	H10F19/80	NEW
H10F 19/85	H10F 19/85	NEW
H10F 19/90	H10F 19/90	NEW
H10F 19/902	H10F 19/90	NEW
H10F 19/904	H10F 19/90	NEW
H10F 19/906	H10F 19/90	NEW
H10F 19/908	H10F 19/90	NEW
H10F 30/00	H10F 30/00	NEW
H10F 30/10	H10F 30/10	NEW
H10F 30/15	H10F 30/10	NEW
H10F 30/20	H10F 30/20	NEW
H10F 30/21	H10F 30/21	NEW
H10F 30/22	H10F 30/22	NEW
H10F 30/2205	H10F 30/22	NEW
H10F 30/221	H10F 30/221	NEW
H10F 30/2212	H10F 30/221	NEW
H10F 30/2215	H10F 30/221	NEW
H10F 30/2218	H10F 30/221	NEW
H10F 30/222	H10F 30/222	NEW
H10F 30/223	H10F 30/223	NEW
H10F 30/2235	H10F 30/223	NEW
H10F 30/225	H10F 30/225	NEW
H10F 30/2255	H10F 30/225	NEW
H10F 30/227	H10F 30/227	NEW
H10F 30/2275	H10F 30/227	NEW
H10F 30/24	H10F 30/24	NEW
H10F 30/245	H10F 30/24	NEW
H10F 30/26	H10F 30/26	NEW
H10F 30/263	H10F 30/26	NEW
H10F 30/2635	H10F 30/26	NEW
H10F 30/28	H10F 30/28	NEW
H10F 30/282	H10F 30/282	NEW
H10F 30/2823	H10F 30/28	NEW
H10F 30/283	H10F 30/28	NEW
H10F 30/2837	H10F 30/28	NEW
H10F 30/2843	H10F 30/28	NEW
H10F 30/285	H10F 30/28	NEW
H10F 30/2857	H10F 30/28	NEW
H10F 30/2863	H10F 30/28	NEW
H10F 30/287	H10F 30/28	NEW
H10F 30/2873	H10F 30/28	NEW
H10F 30/2877	H10F 30/28	NEW
H10F 30/288	H10F 30/21	NEW
H10F 30/289	H10F 30/21	NEW
H10F 30/29	H10F 30/29	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 30/292	H10F 30/292	NEW
H10F 30/2925	H10F 30/292	NEW
H10F 30/295	H10F 30/295	NEW
H10F 30/2955	H10F 30/295	NEW
H10F 30/298	H10F 30/298	NEW
H10F 30/301	H10F 30/00	NEW
H10F 39/00	H10F 39/00	NEW
H10F 39/011	H10F 39/00	NEW
H10F 39/014	H10F 39/00	NEW
H10F 39/016	H10F 39/00	NEW
H10F 39/018	H10F 39/00	NEW
H10F 39/021	H10F 39/00	NEW
H10F 39/022	H10F 39/00	NEW
H10F 39/024	H10F 39/00	NEW
H10F 39/026	H10F 39/00	NEW
H10F 39/028	H10F 39/00	NEW
H10F 39/10	H10F 39/10	NEW
H10F 39/103	H10F 39/10	NEW
H10F 39/107	H10F 39/10	NEW
H10F 39/12	H10F 39/12	NEW
H10F 39/15	H10F 39/15	NEW
H10F 39/151	H10F 39/15	NEW
H10F 39/1515	H10F 39/15	NEW
H10F 39/152	H10F 39/15	NEW
H10F 39/153	H10F 39/15	NEW
H10F 39/1532	H10F 39/15	NEW
H10F 39/1534	H10F 39/15	NEW
H10F 39/1536	H10F 39/15	NEW
H10F 39/1538	H10F 39/15	NEW
H10F 39/154	H10F 39/15	NEW
H10F 39/156	H10F 39/15	NEW
H10F 39/157	H10F 39/15	NEW
H10F 39/1575	H10F 39/15	NEW
H10F 39/158	H10F 39/15	NEW
H10F 39/159	H10F 39/15	NEW
H10F 39/18	H10F 39/18	NEW
H10F 39/182	H10F 39/18	NEW
H10F 39/1825	H10F 39/18	NEW
H10F 39/184	H10F 39/18	NEW
H10F 39/1843	H10F 39/18	NEW
H10F 39/1847	H10F 39/18	NEW
H10F 39/186	H10F 39/18	NEW
H10F 39/1865	H10F 39/18	NEW
H10F 39/189	H10F 39/18	NEW
H10F 39/1892	H10F 39/18	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 39/1895	H10F 39/18	NEW
H10F 39/1898	H10F 39/18	NEW
H10F 39/191	H10F 39/12	NEW
H10F 39/192	H10F 39/12	NEW
H10F 39/193	H10F 39/12	NEW
H10F 39/1935	H10F 39/12	NEW
H10F 39/194	H10F 39/12	NEW
H10F 39/1945	H10F 39/12	NEW
H10F 39/195	H10F 39/12	NEW
H10F 39/196	H10F 39/12	NEW
H10F 39/197	H10F 39/12	NEW
H10F 39/198	H10F 39/12	NEW
H10F 39/199	H10F 39/12	NEW
H10F 39/80	H10F 39/00	NEW
H10F 39/802	H10F 39/00	NEW
H10F 39/8023	H10F 39/00	NEW
H10F 39/8027	H10F 39/00	NEW
H10F 39/803	H10F 39/00	NEW
H10F 39/8033	H10F 39/00	NEW
H10F 39/8037	H10F 39/00	NEW
H10F 39/80373	H10F 39/00	NEW
H10F 39/80377	H10F 39/00	NEW
H10F 39/804	H10F 39/00	NEW
H10F 39/805	H10F 39/00	NEW
H10F 39/8053	H10F 39/00	NEW
H10F 39/8057	H10F 39/00	NEW
H10F 39/806	H10F 39/00	NEW
H10F 39/8063	H10F 39/00	NEW
H10F 39/8067	H10F 39/00	NEW
H10F 39/807	H10F 39/00	NEW
H10F 39/809	H10F 39/00	NEW
H10F 39/811	H10F 39/00	NEW
H10F 39/812	H10F 39/00	NEW
H10F 39/813	H10F 39/00	NEW
H10F 39/90	H10F 39/90	NEW
H10F 39/95	H10F 39/95	NEW
H10F 55/00	H10F 55/00	NEW
H10F 55/10	H10F 55/10	NEW
H10F 55/15	H10F 55/15	NEW
H10F 55/155	H10F 55/155	NEW
H10F 55/16	H10F 55/10	NEW
H10F 55/165	H10F 55/10	NEW
H10F 55/17	H10F 55/10	NEW
H10F 55/18	H10F 55/00	NEW
H10F 55/20	H10F 55/20	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 55/205	H10F 55/20	NEW
H10F 55/207	H10F 55/20	NEW
H10F 55/208	H10F 55/20	NEW
H10F 55/25	H10F 55/25	NEW
H10F 55/255	H10F 55/255	NEW
H10F 55/26	H10F 55/20	NEW
H10F 71/00	H10F 71/00	NEW
H10F 71/10	H10F 71/10	NEW
H10F 71/103	H10F 71/10	NEW
H10F 71/1035	H10F 71/10	NEW
H10F 71/107	H10F 71/10	NEW
H10F 71/121	H10F 71/00	NEW
H10F 71/1212	H10F 71/00	NEW
H10F 71/1215	H10F 71/00	NEW
H10F 71/1218	H10F 71/00	NEW
H10F 71/1221	H10F 71/00	NEW
H10F 71/1224	H10F 71/00	NEW
H10F 71/125	H10F 71/00	NEW
H10F 71/1253	H10F 71/00	NEW
H10F 71/1257	H10F 71/00	NEW
H10F 71/127	H10F 71/00	NEW
H10F 71/1272	H10F 71/00	NEW
H10F 71/1274	H10F 71/00	NEW
H10F 71/1276	H10F 71/00	NEW
H10F 71/1278	H10F 71/00	NEW
H10F 71/128	H10F 71/00	NEW
H10F 71/129	H10F 71/00	NEW
H10F 71/131	H10F 71/00	NEW
H10F 71/132	H10F 71/00	NEW
H10F 71/133	H10F 71/00	NEW
H10F 71/134	H10F 71/00	NEW
H10F 71/135	H10F 71/00	NEW
H10F 71/136	H10F 71/00	NEW
H10F 71/137	H10F 71/00	NEW
H10F 71/1375	H10F 71/00	NEW
H10F 71/138	H10F 71/00	NEW
H10F 71/1385	H10F 71/00	NEW
H10F 71/139	H10F 71/00	NEW
H10F 71/1395	H10F 71/00	NEW
H10F 77/00	H10F 77/00	NEW
H10F 77/10	H10F 77/10	NEW
H10F 77/12	H10F 77/12	NEW
H10F 77/121	H10F 77/121	NEW
H10F 77/1215	H10F 77/121	NEW
H10F 77/122	H10F 77/122	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 77/1223	H10F 77/1223	NEW
H10F 77/1226	H10F 77/1226	NEW
H10F 77/1227	H10F 77/1226	NEW
H10F 77/1228	H10F 77/122	NEW
H10F 77/123	H10F 77/123	NEW
H10F 77/1233	H10F 77/123	NEW
H10F 77/1237	H10F 77/123	NEW
H10F 77/124	H10F 77/124	NEW
H10F 77/1243	H10F 77/124	NEW
H10F 77/1246	H10F 77/124	NEW
H10F 77/1248	H10F 77/124	NEW
H10F 77/12485	H10F 77/124	NEW
H10F 77/126	H10F 77/12	NEW
H10F 77/1265	H10F 77/12	NEW
H10F 77/127	H10F 77/12	NEW
H10F 77/1275	H10F 77/12	NEW
H10F 77/128	H10F 77/12	NEW
H10F 77/1285	H10F 77/12	NEW
H10F 77/14	H10F 77/14	NEW
H10F 77/143	H10F 77/14	NEW
H10F 77/1433	H10F 77/14	NEW
H10F 77/1437	H10F 77/14	NEW
H10F 77/146	H10F 77/14	NEW
H10F 77/1462	H10F 77/14	NEW
H10F 77/1465	H10F 77/14	NEW
H10F 77/1468	H10F 77/14	NEW
H10F 77/147	H10F 77/14	NEW
H10F 77/148	H10F 77/14	NEW
H10F 77/16	H10F 77/16	NEW
H10F 77/162	H10F 77/162	NEW
H10F 77/1625	H10F 77/162	NEW
H10F 77/164	H10F 77/164	NEW
H10F 77/1642	H10F 77/164	NEW
H10F 77/1645	H10F 77/164	NEW
H10F 77/1648	H10F 77/164	NEW
H10F 77/166	H10F 77/166	NEW
H10F 77/1662	H10F 77/166	NEW
H10F 77/1665	H10F 77/166	NEW
H10F 77/1668	H10F 77/166	NEW
H10F 77/169	H10F 77/169	NEW
H10F 77/1692	H10F 77/169	NEW
H10F 77/1694	H10F 77/169	NEW
H10F 77/1696	H10F 77/169	NEW
H10F 77/1698	H10F 77/169	NEW
H10F 77/1699	H10F 77/169	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 77/20	H10F 77/20	NEW
H10F 77/206	H10F 77/20	NEW
H10F 77/211	H10F 77/20	NEW
H10F 77/215	H10F 77/20	NEW
H10F 77/219	H10F 77/20	NEW
H10F 77/223	H10F 77/20	NEW
H10F 77/227	H10F 77/20	NEW
H10F 77/241	H10F 77/20	NEW
H10F 77/244	H10F 77/20	NEW
H10F 77/247	H10F 77/20	NEW
H10F 77/251	H10F 77/20	NEW
H10F 77/254	H10F 77/20	NEW
H10F 77/30	H10F 77/30	NEW
H10F 77/306	H10F 77/30	NEW
H10F 77/311	H10F 77/30	NEW
H10F 77/315	H10F 77/30	NEW
H10F 77/331	H10F 77/30	NEW
H10F 77/334	H10F 77/30	NEW
H10F 77/337	H10F 77/30	NEW
H10F 77/40	H10F 77/40	NEW
H10F 77/407	H10F 77/40	NEW
H10F 77/413	H10F 77/40	NEW
H10F 77/42	H10F 77/42	NEW
H10F 77/45	H10F 77/45	NEW
H10F 77/48	H10F 77/48	NEW
H10F 77/484	H10F 77/42	NEW
H10F 77/488	H10F 77/42	NEW
H10F 77/492	H10F 77/42	NEW
H10F 77/496	H10F 77/40	NEW
H10F 77/50	H10F 77/50	NEW
H10F 77/60	H10F 77/60	NEW
H10F 77/63	H10F 77/63	NEW
H10F 77/67	H10F 77/67	NEW
H10F 77/68	H10F 77/63	NEW
H10F 77/70	H10F 77/70	NEW
H10F 77/703	H10F 77/70	NEW
H10F 77/707	H10F 77/70	NEW
H10F 77/80	H10F 77/80	NEW
H10F 77/90	H10F 77/90	NEW
H10F 77/93	H10F 77/00	NEW
H10F 77/933	H10F 77/00	NEW
H10F 77/935	H10F 77/00	NEW
H10F 77/937	H10F 77/00	NEW
H10F 77/939	H10F 77/00	NEW
H10F 77/95	H10F 77/00	NEW

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>CPC</u>	<u>IPC</u>	<u>Action*</u>
H10F 77/953	H10F 77/00	NEW
H10F 77/955	H10F 77/00	NEW
H10F 77/957	H10F 77/00	NEW
H10F 77/959	H10F 77/00	NEW
H10F 99/00	H10F 99/00	NEW

* Action column:

- For an (N) or (Q) entry, provide an IPC symbol and complete the Action column with “NEW.”
- For an existing CPC main trunk entry or indexing entry where the existing IPC symbol needs to be changed, provide an updated IPC symbol and complete the Action column with “UPDATED.”
- For a (D) CPC entry or indexing entry complete the Action column with “DELETE.” IPC symbol does not need to be included in the IPC column.
- For an (N) 2000 series CPC entry which is positioned within the main trunk scheme (breakdown code) provide an IPC symbol and complete the action column with “NEW”.
- For an (N) 2000 series CPC entry positioned at the end of the CPC scheme (orthogonal code), with no IPC equivalent, complete the IPC column with “CPCONLY” and complete the action column with “NEW”.

NOTES:

- F symbols are not included in the CICL table above.
- T and M symbols are not included in the CICL table above unless a change to the existing IPC is desired.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

5. CROSS-REFERENCE LIST (CRL)

Scheme references impacted by this revision project

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action; New reference symbol; New text</u>
G06E 3/001	H01L 27/14	<u>Delete</u> the entire reference
E04D 3/40	H01L 31/00	<u>Delete</u> the entire reference
F21S 11/00	H01L 31/00	<u>Delete</u> the entire reference so that the title appears as follows: Non-electric lighting devices or systems using daylight {(hybrid lighting devices combining artificial and natural light F21S 19/00; roofs with sky-light opening E04D 13/03; sun blinds for windows with means for redirecting light onto ceiling of a room E06B 9/00; solar heat collectors F24S)}
G01T 1/241	H01L 31/00	<u>Delete</u> the entire reference
G01T 1/26	H01L 31/00	<u>Delete</u> the entire reference
G01T 1/38	H01L 31/00	<u>Delete</u> the entire reference
G01T 3/006	H01L 31/00	<u>Delete</u> the entire reference so that the title appears as follows: {using self-powered detectors (for neutrons as well as for Y- or X-rays), e.g. using Compton-effect (Compton diodes) or photo-emission or a (n,B) nuclear reaction (radioisotopic generators G21H 1/00, e.g. G21H 1/02, G21H 1/04; photo-tubes H01J 40/00; thermionic generators H01J 45/00)}
H01C 7/00	H01L 29/00	H10D1/40-H10D1/43, H10K10/10
H01C 7/00	H01L 31/00	H10F30/00
H01L 21/02365	H01L 31/00	<u>Delete</u> the entire reference
H01L 21/64	H01L31/00-H10K99/00	<u>Replace</u> “groups H01L31/00-H10K99/00” with: “subclasses H10F, H10H, H10K or H10N”

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action: New reference symbol: New text</u>
H01L21/77	H10B69/00	<p><u>Replace</u> with the following revised title:</p> <p>Manufacture or treatment of devices consisting of a plurality of solid state components or integrated circuits formed in, or on, a common substrate (manufacture or treatment of electronic memory devices H10B)</p>
H01L21/77 (Note)	<p>Integration processes for the manufacture of devices of the type classified in H01L 27/14, H01L 27/15, H10N 19/00, H10N 39/00, H10N 59/00, H10N 79/00, H10N 89/00, H10K 19/00, H10K 39/00, H10K 59/00 and H10K 65/00 are not classified in this group and its sub-groups. Instead, as they are peculiar to said devices, they are classified together with the devices</p> <p>Multistep processes for manufacturing memory structures in general using field effect technology are covered by H10B 99/00; Multistep processes for manufacturing dynamic random access memory structures are covered by H10B 12/01; Multistep processes for manufacturing static random access memory structures are covered by H10B 10/00; Multistep processes for manufacturing read-only memory structures are covered by H10B 20/00; Multistep processes for manufacturing electrically programmable read-only memory structures are covered by H10B 69/00</p>	<p><u>Delete</u> the entire Note.</p>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action: New reference symbol: New text</u>
H01L23/00 (note)	<p>This group does not cover:</p> <ul style="list-style-type: none"> • details of semiconductor bodies or of electrodes of devices provided for in group H01L 29/00, which details are covered by that group; • details peculiar to devices provided for in a single main group of groups H01L 31/00, H01L 33/00, H10K 30/00, H10K 50/00, H10K 59/00, H10K 71/00, H10K 85/00, H10K 99/00, H10N 10/00, H10N 30/00, H10N 35/00, H10N 50/00, H10N 52/00, H10N 60/00, which details are covered by those groups. 	<p><u>Replace</u> the existing text with the following revised text:</p> <p>This group does not cover:</p> <ul style="list-style-type: none"> • details of semiconductor bodies or of electrodes of devices provided for in subclass H10D, which details are covered by that group; • details peculiar to devices provided for in a single subclass of subclasses H10F, H10H, H10K or H10N, which details are covered by those places.
H01L24/00 (note)	<p>This group does not cover:</p> <ul style="list-style-type: none"> • details of semiconductor bodies or of electrodes of devices provided for in group H01L 29/00, which details are covered by that group; • details peculiar to devices provided for in a single main group of groups H01L 31/00, H01L 33/00, H10K 30/00, H10K 50/00, H10K 59/00, H10K 71/00, H10K 85/00, H10K 99/00, H10N 10/00, H10N 30/00, H10N 35/00, H10N 50/00, H10N 52/00, H10N 60/00, which details are covered by those groups. 	<p><u>Replace</u> the existing text with the following revised text:</p> <p>This group does not cover:</p> <ul style="list-style-type: none"> • details of semiconductor bodies or of electrodes of devices provided for in subclass H10D, which details are covered by that group; • details peculiar to devices provided for in a single subclass of subclasses H10F, H10H, H10K or H10N, which details are covered by those places.
H01L25/00	<p>Assemblies consisting of a plurality of individual semiconductor or other solid state devices {; Multistep manufacturing processes thereof}; (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00; photovoltaic modules or arrays of photovoltaic cells H01L 31/042 {; panels or arrays of photo electrochemical cells H01G 9/2068})</p>	<p><u>Replace</u> with the following revised title:</p> <p>Assemblies consisting of a plurality of semiconductor or other solid state devices (devices consisting of a plurality of solid-state components formed in or on a common substrate H10D 89/00; photovoltaic modules or arrays of photovoltaic cells H10F 19/00)</p>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action: New reference symbol; New text</u>
H01L 25/041	H01L 31/00	<u>Replace</u> with the following revised title: {the devices being of a type provided for in subclass H10F}
H01L 25/042	H01L 31/042	H10F19/00
H01M14/00(Note)	semiconductor devices sensitive to light and adapted for the conversion of the energy of such radiation into electrical energy are covered by group H01L 31/00;	<u>Replace</u> the existing text with the following revised text: semiconductor devices sensitive to light and adapted for the conversion of the energy of such radiation into electrical energy are covered by group H10F10/00;
H01M 14/005	H01L 31/00	H10F
H02S	H01L 31/00	H10F
H02S 10/30	H01L 31/00	H10F10/00
H02S 30/00	H01L 31/00	H10F10/00, H10F19/00
H02S 40/22	H01L 31/054	H10F77/42
H02S 40/345	H01L 31/052	H10F77/63
H02S 40/42	H01L 31/052	<u>Delete</u> the entire reference
H02S 40/44	H01L 31/0525	H10F77/67

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<p>H04N (Note)</p>	<p>2. This subclass does not cover:</p> <ul style="list-style-type: none"> • circuits or other parts of systems which form the subject of other subclasses, which are covered by the corresponding subclasses, e.g. H03C, H03F, H03J, H04B, H04H; • systems in which legible alphanumeric or like character forms are analysed according to step (a) of Note (1) to derive an electric signal from which the character is recognised by comparison with stored information, which are covered by subclass G06K; • systems for the direct photographic copying of an original picture in which an electric signal representative of the picture is derived according to the said step (a) and employed to modify the operation of the system, e.g. to control exposure, which are covered by class G03; • systems for the reproduction according to step (b) of Note (1) of pictures comprising alphanumeric or like character forms but involving the production of the equivalent of a signal which would be derived according to the above-mentioned step (a), e.g. by cams, punched card or tape, coded control signal, or other means, which are covered by the subclass for the application, e.g. G01D, G06T, H04L; • systems for the reproduction according to the above-mentioned step (b) of pictures comprising alphanumeric or like character forms and involving the generation according to the above-mentioned step (a) of picture-representative electric signals from a pre-arranged assembly of such characters, or records thereof, forming an integral part of the systems, which are covered by the subclass for the application, e.g. B41B, G06K, 	<p><u>Replace</u> the existing text with the following revised text:</p> <p>2. This subclass does not cover:</p> <ul style="list-style-type: none"> • circuits or other parts of systems which form the subject of other subclasses, which are covered by the corresponding subclasses, e.g. H03C, H03F, H03J, H04B, H04H; • systems in which legible alphanumeric or like character forms are analysed according to step (a) of Note (1) to derive an electric signal from which the character is recognised by comparison with stored information, which are covered by subclass G06K; • systems for the direct photographic copying of an original picture in which an electric signal representative of the picture is derived according to the said step (a) and employed to modify the operation of the system, e.g. to control exposure, which are covered by class G03; • systems for the reproduction according to step (b) of Note (1) of pictures comprising alphanumeric or like character forms but involving the production of the equivalent of a signal which would be derived according to the above-mentioned step (a), e.g. by cams, punched card or tape, coded control signal, or other means, which are covered by the subclass for the application, e.g. G01D, G06T, H04L; • systems for the reproduction according to the above-mentioned step (b) of pictures comprising alphanumeric or like character forms and involving the generation according to the above-mentioned step (a) of picture-representative electric signals from a pre-arranged assembly of such characters, or records thereof, forming an integral part of the systems, which are covered by the subclass for the application, e.g. B41B, G06K, subject to those applications which are covered by this subclass; • printing, duplication or marking processes, or materials or processes
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CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

	<p>subject to those applications which are covered by this subclass;</p> <ul style="list-style-type: none"> • printing, duplication or marking processes, or materials or processes therefor, which are covered by the relevant subclasses, e.g. B41C, B41J, B41M, G03C, G03F, G03G; • {apparatus or methods for taking photographs using light sensitive film for image capture, apparatus/methods for printing, for projecting or viewing images using film stock, photographic film or slides by optical means, e.g. mounting of optical elements, flashes, and their related controls, e.g. exposure, focus, (opto-)mechanical motion blur (anti-shake), cooling, beam shaping;} • {aspects of apparatus or methods for taking photographs using an electronic image sensor [EIS] for image capture, insofar as they correspond to those of said apparatus methods for taking photographs using light sensitive film, i.e. insofar as not peculiar to the presence of the EIS, e.g. mounting of optical elements or flashes not peculiar to the presence of the EIS, and their related controls insofar as they are not peculiar to the presence or use of the EIS, e.g. exposure, focus, (opto-)mechanical motion blur (anti-shake);} • {aspects of apparatus or methods for projecting or viewing images using an electronic spatial light modulator [ESLM], insofar as they correspond to those of said apparatus/methods for projecting or viewing images using film stock, photographic film or slides, i.e. insofar as not peculiar to the presence of the ESLM, e.g. mounting of optical 	<p>therefor, which are covered by the relevant subclasses, e.g. B41C, B41J, B41M, G03C, G03F, G03G;</p> <ul style="list-style-type: none"> • {apparatus or methods for taking photographs using light sensitive film for image capture, apparatus/methods for printing, for projecting or viewing images using film stock, photographic film or slides by optical means, e.g. mounting of optical elements, flashes, and their related controls, e.g. exposure, focus, (opto-)mechanical motion blur (anti-shake), cooling, beam shaping;} • {aspects of apparatus or methods for taking photographs using an electronic image sensor [EIS] for image capture, insofar as they correspond to those of said apparatus methods for taking photographs using light sensitive film, i.e. insofar as not peculiar to the presence of the EIS, e.g. mounting of optical elements or flashes not peculiar to the presence of the EIS, and their related controls insofar as they are not peculiar to the presence or use of the EIS, e.g. exposure, focus, (opto-)mechanical motion blur (anti-shake);} • {aspects of apparatus or methods for projecting or viewing images using an electronic spatial light modulator [ESLM], insofar as they correspond to those of said apparatus/methods for projecting or viewing images using film stock, photographic film or slides, i.e. insofar as not peculiar to the presence of the ESLM, e.g. mounting of optical elements not peculiar to the presence of the ESLM, and their related controls not peculiar to the presence of the ESLM, e.g. cooling, beam shaping, optical keystone correction;} • {(opto-)mechanical image enhancement in printers or projectors, e.g. keystone correction;} • {optical viewfinders;} • {remote control of cameras and projectors insofar as not peculiar to the EIS or ESLM, e.g. not affecting
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CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action: New reference symbol: New text</u>
	<p>elements not peculiar to the presence of the ESLM, and their related controls not peculiar to the presence of the ESLM, e.g. cooling, beam shaping, optical keystone correction;}</p> <ul style="list-style-type: none"> • {(opto-)mechanical image enhancement in printers or projectors, e.g. keystone correction;} • {optical viewfinders;} • {remote control of cameras and projectors insofar not peculiar to the EIS or ESLM, e.g. not affecting their operation, or being based on a generated image signal;} • { optical aspects of camera modules using electronic image sensors and related constructional details (optical elements or arrangements associated with solid state imager structures H01L 27/14625); } • {constructional aspects of projectors, e.g. cooling, beam shaping, light integrating means not peculiar to the ESLM;} 	<p>their operation, or being based on a generated image signal;}</p> <ul style="list-style-type: none"> • {optical aspects of camera modules using electronic image sensors and related constructional details (optical elements or arrangements associated with solid state imager structures H10F 39/806);} • {constructional aspects of projectors, e.g. cooling, beam shaping, light integrating means not peculiar to the ESLM}

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Action: New reference symbol; New text</u>
H04N (Warning)	<p>1. The following IPC groups are not in the CPC scheme. Subject matter for these IPC groups is classified in the following CPC groups:</p> <p>H04N 5/761 covered by H04N 5/782</p> <p>H04N 5/7613 covered by H04N 5/782</p> <p>H04N 5/7617 covered by H04N 5/782</p> <p>H04N 5/922 covered by H04N 5/92</p> <p>H04N 5/924 covered by H04N 5/92</p> <p>H04N 9/815 covered by H04N 9/81</p> <p>2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.</p>	<p>1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:</p> <p>H04N 5/761 covered by H04N 5/782</p> <p>H04N 5/7613 covered by H04N 5/782</p> <p>H04N 5/7617 covered by H04N 5/782</p> <p>H04N 5/922 covered by H04N 5/92</p> <p>H04N 5/924 covered by H04N 5/92</p> <p>H04N 9/815 covered by H04N 9/81</p> <p>2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.</p>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

Definitions references impacted by this revision project

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Action; New reference symbol; New text</u>
B32B 17/00	H01L 31/048	Application-oriented references	<u>Replace</u> with the following: Encapsulations or containers for integrated devices, or assemblies of multiple devices, having photovoltaic cells H10F 19/80
B32B 17/10005	H01L 31/048	Application-oriented references	<u>Replace</u> with the following: Encapsulations or containers for integrated devices, or assemblies of multiple devices, having photovoltaic cells H10F 19/80
B32B 17/10005	H01L 31/048	Relationships with other classification places	H10F19/80
B60H 1/00428	H01L 31/042	Relationships with other classification places	<u>Replace</u> with the following: Photovoltaic modules H10F 19/00
B60L 8/003	H01L 31/00	Informative references	H10F
B60R 16/00	H01L 27/14	Informative references	H10F10/00, H10F19/00
B64G 1/44	H01L 31/00	Informative references	H10F10/00
B64G 1/443	H01L 31/00	Informative references	H10F10/00, H10F19/00
B65B 57/00	H01L 31/00	Informative references	H10F10/00, H10F19/00
C01G9/00	C09K11/00	Informative references	<u>Replace</u> with the following: Luminescent materials C09K11/00

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

C01G 9/00	H01L 31/00, H01L 33/00	Informative references	<u>Delete</u> entire reference (symbols and text).
C01G 15/00	H01L 31/00	Informative references	<u>Delete</u> entire reference (symbol and text).
C01G 17/00	H01L 31/00	Informative references	<u>Delete</u> entire reference (symbol and text).
C01G 23/003	H01L 31/00, H10N60/00	Informative references	<u>Delete</u> entire reference (symbols and text).
C01G 23/005	H01L 31/00, H10N60/00	Informative references	<u>Delete</u> entire reference (symbols and text).
C01G 23/006	H01L 31/00, H10N60/00	Informative references	<u>Delete</u> entire reference (symbols and text).
C03C 8/00	H01L 31/0224	Informative references	<u>Delete</u> entire reference (symbol and text).
C03C 17/00	H01L 31/0216	Informative references	H10F77/30
C04B 35/457	H01L 29/7869	Informative references	H10D30/6755
C04B 35/457	H01L 31/022466, H01L 31/1884, H10K30/82	Informative references	H10F71/138, H10F77/244, H10K30/82
C04B 35/457	M03C 217/598	Informative references	C03C2217/948
C04B 35/565	H01L 31/0312 and subgroups, H01L 31/03687, H01L 31/03765, H01L 31/1816, H01L 31/204	Informative references	H10F71/1218, H10F71/1035 H10F77/1226, H10F77/1648. H10F77/1665,
C04B 35/565	H01L 21/02378, H01L 21/0445 and subgroups,	Informative reference	H01L 21/02378, H01L 21/0445 and subgroups,

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

	H01L 21/8213, H01L 29/1608		H10D62/8325, H10D84/035,
C04B 35/565	H01L29/78684	Informative reference	<u>Replace</u> : "H01L 29/78684 and subgroup" <u>With</u> : "H10D30/6741"
C09J7/00	H01L 31/0488	Application-oriented references	H10F19/85
C09J123/00	H01L 31/048	Informative references	H10F19/80
C09J133/00	H01L 31/048	Informative references	H10F19/80
C09J137/00	H01L 31/048	Informative references	H10F19/80
C09J139/00	H01L 31/048	Informative references	H10F19/80
C09J143/00	H01L 31/048	Informative references	H10F19/80
C09J149/00	H01L 31/048	Informative references	H10F19/80
C09J149/00	Example 3: An adhesive composition based on a composition of polyacetylene and containing CaCO ₃ is classified as (C09J 149/00, C08K 3/26). If this composition contains also a polyamide, then the classification will be (C09J 149/00) C08L 77/00, C08K 3/26).	Special rules of classification	Example 3: An adhesive composition based on a composition of polyacetylene and containing CaCO ₃ is classified as (C09J 149/00, C08K 3/26). If this composition contains also a polyamide, then the classification will be (C09J 149/00) C08L 77/00, C08K 3/26).
C23C 14/00	Trivial references to well known PVD processes are not classified. As an example "...the SiO ₂ layer was deposited by sputtering..." may be mentioned.	Special rules of classification	Trivial references to well-known PVD processes are not classified. As an example, "...the SiO ₂ layer was deposited by sputtering..." may be mentioned.
C23C 14/00	C23C 14/58-C23C 14/5893C23C 14/58 includes a after deposition treatment of a coating or film deposited by the techniques of C23C 14/00.	Special rules of classification	C23C 14/58-C23C 14/5893: C23C 14/58 includes a after deposition treatment of a coating or film deposited by the techniques of C23C 14/00.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

C23C 18/00	H01L 31/00	Informative references	H10F10/00, H10F19/00
C25D	H01L 31/00	Informative references	H10F10/00, H10F19/00
C25D 7/00	H01L 31/00	Informative references	H10F10/00, H10F19/00
C25D 7/126	H01L 31/18	Application-oriented references	H10F71/00
F24F	H01L 31/024	Informative references	H10F77/60
F24S	H01L 31/0525	Application-oriented references	H10F77/67
F24S	H01L 31/00	Informative references	H10F10/00, H10F19/00
F24S90/00	H01L 31/0525	References out of a residual place	H10F77/67
G01B	H01L21/00, H01L 31/00	Informative references	<u>Replace</u> with the following: Semiconductor devices H10
G01J	H01L 27/14, H01L 31/00, H10K30/00	Informative references	<u>Delete</u> entire entry (symbols and text).
G01J	H01L 27/15, H01L 33/00, H10K 50/00	Informative references	H10H, H10K50/00
G01J	H01L27/00, H01L31/00	Limiting references	<u>Delete</u> entry from Limiting references section and <u>move</u> to Informative references table with the following text: Semiconductor devices sensitive to radiation H10F, H10K30/00, H10K39/00
G01J1/04	Solar radiation detectors for controlling protective blades or dimming E06B 9/32, F21S 11/00, F21S23/00, H05B 39/04, G05D 25/02	Informative references	<u>Replace</u> with: Solar radiation detectors for controlling protective blades or dimming E06B 9/32, H05B 39/04, G05D 25/02

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

G01J3/2803	H01L 27/14	Informative references	<u>Replace</u> entry (symbol and text) with: Image sensors H10F39/12
G01J3/2803	H01L 27/14658	Informative references	<u>Delete</u> entire entry (symbol and text).
G01S 7/48	H01L23/00, H01L 31/00	Limiting references	<u>Delete</u> entry from Limiting references section and <u>move</u> to Informative references table with the following text: Details of radiation sensitive semiconductor devices H10F
G01S 7/4816	H01L 31/00	Relationships with other classification places	H10F77/00
G01S7/4816	H01L27/00	Relationships with other classification places	H10F39/80
G01S 7/486	G01J, H01L 31/00, H10K 30/00, H10K39/00	Informative references	G01J, H10F, H10K 30/00, H10K39/00
G01S 7/486	H01J, H01L 31/00, H10K30/00, H10K39/00	Informative references	H01J, H10F10/00, H10F30/00, H10K30/00
G01S 7/486	H01L 27/14	Informative references	H10F39/12
G01S 7/486	H01L 31/101	Informative references	H10F30/20
G01S 7/4861	H01L 27/146	Informative references	H10F39/12, H10F39/15, H10F39/18
G01S 7/4863	H01L 27/146	Informative references	H10F39/12, H10F39/15, H10F39/18
G01S 7/4913	H01L 27/146	Informative references	H10F39/12, H10F39/15, H10F39/18
G01S 7/4914	H01L 27/146	Informative references	H10F39/12, H10F39/15, H10F39/18
G01T	H01L 31/00	Informative references	H10F30/00, H10F39/00

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

G01T 1/00	H01L 31/00	Informative references	<u>Delete</u> text “Semiconductor detectors constructional details and devices” <u>and</u> delete symbol H01L31/00
G01T 1/00	H01L 31/00	Limiting references	<u>Delete</u> entry from Limiting references section and <u>move</u> to Informative references table with the following text: Inorganic semiconductor devices sensitive to radiation H10F30/00, H10F39/00
G01V 8/00	H01L 31/00	Informative references	H10F
G02B	H01L 33/58	Application-oriented references	H10H20/855
G02B	H01L 31/054	Informative references	H10F77/40
G02B 6/12	H01L 31/00	Informative references	H10F30/00
G02B6/12	H01L33/00	Informative references	H10H20/00
G02B6/12	H01L27/00	Limiting reference	H10B, H10D84/00- H10D89/00, H10F19/00, H10F39/00, H10H29/00, H10K19/00, H10K39/00, H10K59/00, H10N19/00 H10N39/00, H10N59/00, H10N69/00, H10N79/00, H10N89/00
G02B 6/42	H01L 31/00	Informative references	H10F
G02B 6/42	H01L 33/00	Informative references	H10H20/00
G02B 6/42	H01L 33/58	Informative references	H10H20/855

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

G02B 6/42	H01L 33/62	Informative references	H10H20/857
G02B 6/43	H01L27/00, H01L 31/00, H01L33/00	Informative references	H10F, H10H
G02B 19/00	H01L 31/0232	Informative references	H10F77/40
G02B 19/00	H01L 33/58	Informative reference	H10H20/855
G02F	H01L 31/00	Informative references	H10F
G02F 1/35	H01L 31/00, H01Q9/00	Informative references	<u>Delete only</u> symbol H01L31/00. Retain symbol H01Q9/00.
G02F 2/00	H01L 31/00	Application-oriented references	H10F
G03B	H01L 27/146	Informative references	H10F39/12
G06V 10/10	H01L 27/146	Informative references	H10F39/12, H10F39/15, H10F39/18
G08G 1/095	H01L 31/00	Informative references	<u>Replace</u> with: Inorganic semiconductor devices sensitive to electromagnetic or corpuscular radiation H10F30/00, H10F39/00
G08G 1/095	H01L 31/042	Informative references	<u>Replace</u> with: Photovoltaic modules H10F19/00
G08G1/16	B60Q 1/48, B60T2201/10	Limiting references	<u>Delete</u> the entire Limiting references section and <u>move</u> to Informative references table as follows: Parking aids B60T2201/10
G21H	H01L 31/00	Informative references	H10F
G21H 1/06	H01L 31/118	Informative references	H10F30/295
G21H 5/00	H01L 31/00	References out of a residual place	H10F

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01C	H01L31/08	Limiting references	<u>Delete</u> from the Limiting references section and <u>move</u> to Informative references table with the following text: Photoresistors and similar semiconductor devices in which radiation controls flow of current through the device H10F30/00
H01C	H01L28/00	Limiting references	<u>Delete</u> entire reference (symbol and text)
H01C	H01L29/00	Limiting references	<u>Delete</u> from the Limiting references section and <u>move</u> to Informative references table with the following text: Resistors having potential barriers, e.g., field-effect resistors H10D1/40-H10D1/43, H10K10/10
H01C	H01L27/00	Application oriented references	<u>Replace</u> with: Resistors as a component of an integrated circuit H10D1/47
H01C7/00	H01L28/20	Informative reference	H10D1/47
H01C7/00	H01L27/00	Informative reference	<u>Delete</u> entire reference (symbol and text)
H01C7/00	H01L31/00	Limiting references	H10F30/00
H01C7/00	H01L29/00	Limiting reference	H10D1/40-H10D1/43
H01G9/20	H01L31/00	Limiting references	<u>Replace</u> with:

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

			Inorganic semiconductor devices sensitive to electromagnetic or corpuscular radiation H10F
H01G9/20	<p>In this group, documents are classified according to the ECLA Reform approach, i.e. "invention information" is identified with ECLA classification symbols, e.g. H01G9/2031, while "additional information" is identified with Indexing Code symbols, e.g. H01G9/2059.</p> <p>In this subclass, Indexing Codes are mainly attributed with a view to allow retrieval of documents comprising a combination of technical characteristics, some of them being unimportant per se, and, hence, identified with an Indexing Code symbol rather than with the corresponding ECLA one potential-jump barrier or surface barrier.</p>	Special Rules of Classification	<p><u>Replace</u> the existing text with the following revised text:</p> <p>In this group, documents are classified according to the inventive information e.g. classification symbol H01G9/2031, while "additional information" is identified with Indexing Code symbols, e.g. H01G9/2059.</p> <p>In this subclass, Indexing Codes are mainly attributed with a view to allow retrieval of documents comprising a combination of technical characteristics, some of them being unimportant per se, and, hence, identified with an Indexing Code symbol rather than with the corresponding potential-jump barrier or surface barrier.</p>
H01J31/00	H01L27/146	Informative references	H10F39/12
H01J31/00	H01L33/00	Informative references	H10H20/00
H01J40/00	H01L31/00	Informative references	<p><u>Replace</u> with:</p> <p>Inorganic semiconductor devices sensitive to electromagnetic or corpuscular radiation</p>

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

			H10F
H01J43/00	H01L31/107	Informative references	H10F30/225
H01L21/00	Processes or apparatus specially adapted for the manufacture or treatment of devices provided for in groups H01L31/00, H01L33/00, H10K30/00, H10K50/00, H10K59/00, H10K71/00, H10K85/00, H10K99/00, H10N10/00, H10N30/00, H10N35/00, H10N50/00, H10N52/00, H10N60/00 H10K99/00 or of parts thereof, see these groups H01L31/00, H01L33/00, H10K30/00, H10K50/00, H10K59/00, H10K71/00, H10K85/00, H10K99/00, H10N10/00, H10N30/00, H10N35/00, H10N50/00, H10N52/00, H10N60/00 H10K99/00	Informative references	<u>Replace</u> with the following new text and symbols: Processes or apparatus specially adapted for the manufacture or treatment of devices or parts thereof H10B, H10D, H10F, H10H, H10K or H10N
H01L21/02365	H01L31/00	Informative references	H10F71/00
H01L21/30608	H01L31/18	Limiting references	H10F71/00
H01L21/34	H01L29/00, H01L31/00	Special rules of classification	<u>Delete</u> the entire Special rules section.
H01L21/38	H01L31/0296	Informative references	H10F77/123
H01L21/77	This place covers: In the group range H01L21/77 - H01L21/86 are classified processes for integration a plurality of solid state components formed in or on a common substrate, with • H01L21/77 and H01L2021/75 covering the manufacturing of devices consisting of a plurality of solid state components formed or assembles ON a common substrate, e.g. integrated circuits formed	Definition statement	<u>Replace</u> the entire existing Definition statement with the following: This place covers: Processes for the division of a substrate into a plurality of individual devices.

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

	of a plurality of chips on a host substrate, and • H01L 21/82 - H01L 21/86 covering the manufacturing of devices consisting of a plurality of solid state components formed IN a common substrate, e.g. integrated circuits formed of a single chip, and • H01L 21/78 - H01L 21/786 being reserved to processes for the division of a substrate into a plurality of individual devices.		
H01L21/77	Informative references	Informative references	<u>Delete</u> the entire Informative references section.
H01L 21/77	Integration processes for the manufacture of devices of the type classified in H01L27/14, H01L 27/15, H10N 19/00, H10N 39/00, H10N 59/00, H10N 79/00, H10N 89/00, H10K 19/00, H10K 39/00, H10K 59/00 and H10K 65/00	Limiting references	<u>Delete</u> the entire entry (symbols and text).
H01L21/77	H10B12/01	Limiting references	H10B
H01L 21/77	Special rules of classification	Special rules of classification	<u>Delete</u> the entire Special rules section.
H01L 21/78	Limiting references	Limiting references	<u>Delete</u> the entire Limiting references section.
H01L 23/00	H01L 29/0657	Informative references	<u>Delete</u> the entire entry (symbols and text).
H01L 23/00	H01L 29/40	Informative references	<u>Delete</u> the entire entry (symbols and text).
H01L 23/00	H01L 29/00	Limiting references	<u>Delete</u> the entire entry (symbols and text).
H01L 23/00	H01L 31/00	Limiting references	<u>Delete</u> the entire entry (symbols and text).
H01L 23/00	Details peculiar to solid state devices not provided for in groups H01L 27/00–H01L 33/00, H10B 10/00–	Limiting references	<u>Delete</u> the entire entry (symbols and text).

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

	H10B 53/00, H10B 69/00, H10K 10/00, H10K 30/00, H10K 50/00, H10K 71/00, H10K 77/00, H10K 85/00 and H10K 99/00 and not provided for in any other subclass		
H01L 23/00	H01L 33/00	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 23/02	H01L 27/14618	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 24/00	H01L 29/00	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 24/00	H01L 31/00	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 24/00	H01L 33/00	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 24/00	Details peculiar to solid state devices not provided for in groups H01L 27/00–H01L 33/00, H10B 10/00–H10B 53/00, H10B 69/00, H10K 10/00, H10K 30/00, H10K 50/00, H10K 71/00, H10K 77/00, H10K 85/00 and H10K 99/00 and not provided for in any other subclass	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01L 25/00	H01L21/06-H01L21/326	Informative references	<u>Delete</u> the entire entry (symbols and text).
H01L 25/00	H01L 27/146	Informative references	H10F39/10
H01L 25/00	H01L 31/0687	Informative references	H10F10/142
H01L 25/00	H01L 31/0725	Informative references	H10F10/161
H01L 25/00	H01L 31/076	Informative references	H10F10/172
H01L 25/00	H01L 31/078	Informative references	H10F10/19
H01L 25/00	H01L 31/12	Informative references	H10F55/00
H01L 25/00	H01L 31/042	Limiting references	H10F19/00

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01L 25/00	H01L 27/00	Limiting references	H10D89/00
H01L 25/042	H01L 31/043	Informative references	<u>Delete</u> this entry
H01L 25/042	H01L 27/14647	Limiting references	<u>Delete</u> from the Limiting references section and <u>move</u> to Informative references table with the following text: Multicolour imagers having a stacked structure H10F39/1825
H01L 25/042	H01L 27/14652	Limiting references	<u>Delete</u> from the Limiting references section and <u>move</u> to Informative references table with the following text: Multispectral infrared imagers, having a stacked structure H10F39/1847
H01L 25/042	H01L 31/042	Limiting references	H10F19/00
H01L 25/18	H01L 27/144	Limiting references	<u>Delete</u> the entire entry (symbol and text).
H01M	H01L 31/00	Informative references	H10F10/00, H10F19/00
H01M 8/00	H01L 31/00	Informative references	H10F10/00, H10F19/00

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H01M 14/005	H01L 31/00	Limiting references	H10F10/00, H10F19/00
H01M 14/005	H01L 31/00	Relationships with other classification places	H10F, H10F10/00, H10F19/00
H01Q 5/22	H01L 27/14	Informative references	<u>Replace</u> with: Integrated devices, or assemblies of multiple devices, comprising at least one light-sensitive inorganic semiconductor device H10F39/00
H01S 1/00	H01L 31/00	Informative references	<u>Delete</u> only the symbol H01L31/00. Retain the rest of the entry.
H01S 1/00	H01L 31/00	Informative references	<u>Delete</u> the symbol H01L31/00 and also <u>insert</u> the following new entry: Inorganic light-emitting semiconductor devices having potential barriers H10F
H01S5/00	H01L33/00	Limiting references	H10H20/042
H01S 5/00	H01L 31/00	Relationships with other classification places	H10F30/00
H01S 5/00	H01L 33/00	Relationships with other classification places	H10H20/00
H01S5/00	H01L27/00	Relationships with other classification places	<u>Delete</u> the entire entry (symbol and text)
H02H 7/00	H01L 31/02021	Informative references	<u>Replace</u> with: Circuit arrangements for photovoltaic devices H10F77/955

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H02H 7/20	H01L 31/042, H01L 31/02021	Limiting references	<u>Delete</u> entire entry from the Limiting references section and <u>move</u> to the Informative references section with the following text and symbol: Circuit arrangements for photovoltaic devices H10F77/955
H02J	H01L 31/00	Informative references	H10F10/00, H10F19/00
H02J 3/00	H01L 31/00	Informative references	<u>Replace</u> with: Photovoltaic modules H10F19/00
H02S	H01L 31/00	Limiting references	H10F
H02S 10/20	H01L 31/053	Informative references	H10F77/90
H02S 10/30	H01L 31/00	Limiting references	H10F10/00
H02S 10/30	H01L 31/06	Relationships with other classification places	H10F10/10
H02S 10/30	H01L 31/068	Relationships with other classification places	H10F10/10
H02S 30/00	H01L 31/00	Limiting references	H10F10/00, H10F19/00
H02S 40/22	H01L 31/054	Limiting references	H10F77/42
H02S 40/36	H01L 31/022425	Informative references	H10F77/20
H02S 40/36	H01L 31/0465	Informative references	H10F19/35
H02S 40/36	H01L 31/05	Informative references	H10F19/85
H02S 40/42	H01L 31/052	Limiting references	<u>Delete</u> from the Limiting references section and <u>move</u> to the Informative references table with the following text:

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

			Cooling means directly associated or integrated with the PV cell H10F77/63
H02S 40/44	H01L 31/0525	Limiting references	H10F77/67
H04B 10/00	H01L 31/00	Informative references	H10F
H04N 5/455	H01L 27/06	Informative reference	<u>Delete</u> this reference symbol
H04N 5/455	H01L 27/14	Informative references	<u>Replace</u> with H04L 27/06, H04L 27/14, H04L 27/22, H04L 27/38
H04N 5/455	H10B 61/00	Informative references	<u>Delete</u> only the symbol H10B 61/00. Retain the rest of the entry.
H04N 23/00	H01L 27/146	Informative references	H10F 39/12, H10F 39/18
H04N 23/00	H01L 27/148	Informative references	H10F 39/15
H04N 25/00	H01L 27/146	Informative references	H10F 39/12, H10F 39/18
H04N 25/00	H01L 27/148	Informative references	H10F 39/15
H04N 25/00	H01L 27/00	Relationships with other classification places	Replace “the groups in main group H10L 27/00” with “the groups H10F 39/12, H10F 39/15, H10F 39/18 and H10K 39/32”
H04N 25/21	H01L 27/144	Informative references	H10F 39/10
H04N 25/70	H01L 27/146	Informative references	H10F 39/12, H10F 39/15, H10F 39/18
H04N 25/702	H01L 27/146	Informative references	H10F 39/12, H10F 39/15, H10F 39/18
H04N 25/71	H01L 27/148	Informative references	H10F 39/15
H04N 25/76	H01L 27/146	Informative references	H10F 39/12, H10F 39/18

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

H04N 25/76	H01L 27/148	Informative references	H10F39/15
H04N 25/773	H01L 31/107	Informative references	H10F30/225
H05B 33/00	H01L 31/14	Informative references	<u>Delete</u> entire entry (symbol and text).
H05B 33/00	H01L 27/15, H01L 33/00	Informative references	H10H 20/00, H10H 29/00
H05K1/00	H01L	Informative references	<u>Replace</u> with: Semiconductor devices per se and integrated devices consisting of a plurality of semiconductor or active solid-state devices H10
H05K1/00	H01L21/48, H01L23/00	Informative references	H01L 21/48, H01L 23/00, H01L 24/00
H05K 1/00	H01L 31/00	Informative references	<u>Delete</u> entire entry (symbol and text).
H05K 1/00	H01L 33/00	Informative references	<u>Delete</u> entire entry (symbol and text).
H05K 1/00	H01L 27/00	Informative references	Delete entire entry (symbol and text).
H05K1/00	H01L27/01	Application-oriented references	Delete entire entry (symbol and text).
H05K 1/00	H04N, H01L 27/00, G03B	Informative references	H04N, G03B
H05K1/00	H01L	Relationships with other classification places	H01L, H10
H05K 1/00	H01L 27/00	Relationships with other classification places	<u>Delete</u> the text: “thin film and thick film circuits (H01L 27/00),”
H05K 7/20	H01L 31/052	Application-oriented references	H10F77/63
H05K 7/20	H01L 33/64	Application-oriented references	H10H20/858
H10K 30/00	H01L 31/00	Informative references	H10F
H10K 39/00	H01L 27/14	Informative references	<u>Replace</u> with: Integrated devices comprising inorganic

CPC NOTICE OF CHANGES 1722

DATE: JANUARY 1, 2025

PROJECT RP12333

			radiation-sensitive components H10F19/00, H10F39/00
H10K 39/00	H01L 27/02	Informative references	H10D84/00- H10D89/00
H10K 39/00	H01L 27/142	Informative references	<u>Delete</u> entire entry (symbol and text).
H10K 39/00	H01L 27/144	Informative references	<u>Delete</u> entire entry (symbol and text).
H10K 65/00	H01L 31/12	Informative references	H10F55/00
H10N 10/00	H01L 31/052	Informative references	H10F77/63
H10N 15/00	H01L 31/052	Informative references	H10F77/63
H10N 15/00	H01L 31/09	Informative references	H10F30/10
H10N 15/00	H01L 31/101	Informative references	H10F30/20, H10F30/22
H10N 19/00	H01L 31/052	Informative references	H10F77/63

NOTES:

- The CRL tables above are used for changes to locations **outside** of the project scope. Changes to references in scheme titles or definitions **inside** the project scope will be reflected in the “scheme change” template or one of the “definition” templates.
- In addition to other changes proposed in the tables above, in the column titled “Referenced subclass or group to be changed,” **referenced** D symbols should indicate an action of “delete” or should indicate a replacement symbol and **referenced** F symbols should indicate a replacement symbol.
- When a reference is deleted, text related to that reference will also be deleted unless other references or a range of references associated with the same text remain.